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July 20, 2000

BOX PATENT APPLICATION
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Re: New U.S. Patent Application
IMAGE-SENSING APPARATUS
By: Yoshio HAGIHARA
Attorney Docket: 15162/02240

Dear Sir:

Enclosed for filing are the following papers relating to
IMAGE-SENSING APPARATUS, Yoshio HAGIHARA, inventor:

- (1) Specification;
- (2) Executed Declaration and Power of Attorney;
- (3) Formal Drawings (15 sheets);
- (4) Transmittal of PrintEFS Patent Application
Bibliographic Data;
- (5) Certified Copy of Priority Document;

Assistant Director For Patents
July 20, 2000
Page 2

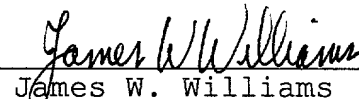
- (6) Information Disclosure Statement, with PTO-1449 Form and copies of cited references;
- (7) Assignment of the invention to MINOLTA CO., LTD., with attached Recordation Form Cover Sheet;
- (8) Check in the amount of \$40.00 to cover the fee for recordal of Assignment; and
- (9) Check in the amount of \$762.00 to cover the filing fee of the application.

In the event the attached checks in the amounts of \$40.00 and \$762.00 are not received with this correspondence, are not sufficient, or in the event additional fees are due, please charge the required fees during the pendency of this application (other than issue fee) to Sidley & Austin's Deposit Account No. 18-1260. Please credit any overpayment to Sidley & Austin's Deposit Account No. 18-1260.

All correspondence is to be directed to the Applicant's attorney at the Dallas address listed above.

Respectfully submitted,

By:



James W. Williams
Registration No. 20,047
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JWW:pm
Enclosures

Attorney Docket No. 15162/02240

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re

U.S. application of: Yoshio HAGIHARA
For: IMAGE-SENSING APPARATUS
U.S. Serial No.: To Be Assigned
Filed: Concurrently
Group Art Unit: To Be Assigned
Examiner: To Be Assigned

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for Patents
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Patents, Washington, DC 20231

Derrick T. Gordon

Name of Person Mailing Paper or Fee

Derrick T. Gordon

Signature

July 20, 2000

Date of Signature


Dear Sir:

TRANSMITTAL OF PrintEFS PATENT APPLICATION

BIBLIOGRAPHIC DATA

Submitted herewith is bibliographic data (2 pages) for
the above-identified application, in the PrintEFS Version
1.0.1 program format.

Respectfully submitted,



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APPLICATION INFORMATION

Title Line One:: IMAGE-SENSING APPARATUS
Total Drawing Sheets:: 15
Formal Drawings?: Yes
Application Type:: Utility
Docket Number:: 15162/02240
Secrecy Order in Parent Appl.?: No

REPRESENTATIVE INFORMATION

Registration Number One:: 39095
Registration Number Two:: 27189
Registration Number Three:: 37803
Registration Number Four:: 38425
Registration Number Five:: 29160
Registration Number Six:: 30067
Registration Number Seven:: 44196

IMAGE-SENSING APPARATUS

This application is based on application No. H11-207411 filed in Japan on July 22, 1999, the entire contents of which are hereby incorporated by reference.

5

BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates to an image-sensing apparatus, and particularly to an image-sensing apparatus incorporating a solid-state image-sensing device having a plurality of pixels arranged therein.

10

Description of the Prior Art

Solid-state image-sensing devices designed for use in image-sensing apparatuses are not only small-sized, light-weight, and power-saving, but also free from image distortion, free from image burn-in, and resistant to unfavorable environmental conditions such as vibration and electric fields. Moreover, such image-sensing devices can be manufactured by a process common or analogous to one used to manufacture LSIs (large-scale integrated circuits), and therefore they are reliable and fit for mass production. For these reasons, solid-state image-sensing devices having pixels arranged in a line are widely used in facsimile machines, flat-bed scanners, and the like, and solid-state image-sensing devices having pixels arranged in a matrix are widely used in video cameras, digital cameras, and the like. Solid-state image-sensing devices are roughly grouped into two types according to the means they use to read out (extract) the photoelectric

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charges generated in their photoelectric conversion devices, namely a CCD type and a MOS type. A CCD-type image-sensing device accumulates photoelectric charges in potential wells while transferring them, and has the disadvantage of a comparatively narrow dynamic range. On the other hand, a MOS-type image-sensing device reads out electric charges accumulated in the pn-junction capacitances of photodiodes through MOS transistors.

Now, how each pixel is configured in a conventional MOS-type solid-state image-sensing device will be described with reference to Fig. 21. As shown in this figure, a photodiode PD has its cathode connected to the gate of a MOS transistor T101 and to the source of a MOS transistor T102. The MOS transistor T101 has its source connected to the drain of a MOS transistor T103, and this MOS transistor T103 has its source connected to an output signal line VOUT. A direct-current voltage VPD is applied to the drain of the MOS transistor T101 and to the drain of the MOS transistor T102, and a direct-current voltage VPS is applied to the anode of the photodiode.

When light enters the photodiode PD, a photoelectric charge is generated therein, and this electric charge is accumulated at the gate of the MOS transistor T101. Here, when a pulse signal ϕV is fed to the gate of the MOS transistor T103 to turn this MOS transistor T103 on, a current proportional to the electric charge accumulated at the gate of the MOS transistor T101 flows through the MOS transistors T101 and T103 to the output signal line VOUT. In this way, it is possible to read an output current that is proportional to the amount of incident light. After this signal has been read, the MOS transistor T103 is turned off and a signal ϕRS is fed to the gate of the MOS transistor T102 to turn the MOS transistor

T102 on so that the gate voltage of the MOS transistor T101 will be initialized.

As described above, in a conventional MOS-type solid-state image-sensing device, at each pixel, the photoelectric charge generated in the photodiode PD and then accumulated at the gate of the MOS transistor T101 is directly read out. This, however, leads to a narrow dynamic range and thus demands accurate control of the amount of exposure. Moreover, even if the amount of exposure is controlled accurately, the obtained image tends to suffer from flat blackness in dim portions thereof and saturation in bright portions thereof.

On the other hand, the assignee of the present invention has once proposed a solid-state image-sensing device including a light-sensing means that generates a photoelectric current in accordance with the amount of incident light, a MOS transistor to which the generated photoelectric current is fed, and a bias-supplying means that supplies a bias to the MOS transistor to bring it into a state in which a subthreshold current flows therethrough so that the photoelectric current is subjected to logarithmic conversion (refer to United States Patent No. 5,241,575). This solid-state image-sensing device offers a wide dynamic range, but tends to suffer from different threshold-value characteristics among the MOS transistors provided in the individual pixels and thus varying sensitivity from one pixel to another. To overcome this, the outputs from the individual pixels in actual shooting of a subject need to be corrected by using compensation data that is stored beforehand by reading the outputs from the pixels with the pixels illuminated with uniformly bright light (uniform light).

However, it is troublesome for a user to illuminate the pixels with an external light source, and moreover it is difficult to illuminate them sufficiently

sensing apparatus according to the invention;

Fig. 2 is a block circuit diagram illustrating the overall configuration of a two-dimensional solid-state image-sensing device embodying the invention;

Fig. 3 is a circuit diagram showing the configuration of each pixel in a first embodiment of the invention;

Figs. 4A, 4B, and 4C are diagrams showing the structure of and the potential relationship observed in a pixel according to the invention;

Figs. 5A, 5B, and 5C are diagrams showing the potential relationship observed in a pixel according to the invention;

Fig. 6 is a block circuit diagram illustrating the overall configuration of another two-dimensional solid-state image-sensing device embodying the invention;

Figs. 7A and 7B are circuit diagrams of a portion of the circuit shown in Fig. 6;

Fig. 8 is a circuit diagram showing the configuration of each pixel in a second embodiment of the invention;

Fig. 9 is a circuit diagram showing the configuration of each pixel in a third embodiment of the invention;

Fig. 10 is a circuit diagram showing the configuration of each pixel in a fourth embodiment of the invention;

Fig. 11 is a circuit diagram showing the configuration of each pixel in a fifth embodiment of the invention;

Fig. 12 is a block circuit diagram illustrating the overall configuration of a two-dimensional solid-state image-sensing device embodying the invention, in a

case where the active elements within a pixel are composed of P-channel MOS transistors;

Fig. 13 is a circuit diagram showing the configuration of each pixel in a sixth embodiment of the invention;

5 Fig. 14 is a block circuit diagram illustrating the overall configuration of another two-dimensional solid-state image-sensing device embodying the invention, in a case where the active elements within a pixel are composed of P-channel MOS transistors;

 Figs. 15A and 15B are circuit diagrams of a portion of the circuit shown in

10 Fig. 14;

 Fig. 16 is a circuit diagram showing the configuration of each pixel in a seventh embodiment of the invention;

 Fig. 17 is a circuit diagram showing the configuration of each pixel in an eighth embodiment of the invention;

15 Fig. 18 is a circuit diagram showing the configuration of each pixel in a ninth embodiment of the invention;

 Fig. 19 is a circuit diagram showing the configuration of each pixel in a tenth embodiment of the invention;

 Fig. 20 is a block diagram showing the internal configuration of an image
20 input apparatus provided with an image-sensing apparatus having pixels configured according to one of the embodiments of the invention; and

 Fig. 21 is a circuit diagram showing the configuration of each pixel in a conventional solid-state image-sensing device.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Image-Sensing Apparatus

First, an image-sensing apparatus according to the present invention will be described with reference to the drawings. Fig. 1 is a block diagram showing the internal configuration of an image-sensing apparatus according to the invention. The image-sensing apparatus 52 shown in Fig. 1 includes the following components. A solid-state image-sensing device 1 receives the light from a subject through an objective lens 51. A controller 100 controls the operation of the solid-state image-sensing device 1. A processor 101 checks whether the output of the solid-state image-sensing device 1 is compensation data or image data, and outputs it.

In this image-sensing apparatus 52 configured as described above, the controller 100, by switching the voltage of a signal ϕVPS fed to the individual pixels provided in the solid-state image-sensing device 1, switches the photoelectric conversion operation of the individual pixels between logarithmic conversion and linear conversion. Moreover, the controller 100, by feeding a pulse signal ϕV to the individual pixels, makes them feed the electric signals obtained as image data or compensation data as a result of photoelectric conversion to the processor 101. Moreover, after the individual pixels have output image data, the controller 100, by switching the states of signals ϕVPS , ϕSW , ϕV , ϕD , and ϕVRS with predetermined timing, resets the pixels and makes them output compensation data. The signals ϕVPS , ϕSW , ϕV , ϕD , and ϕVRS fed to the individual pixels of the solid-state image-sensing device 1 will be described later.

In this way, the solid-state image-sensing device 1 is controlled by the

controller 100 by being fed with various signals as mentioned above. The output of the solid-state image-sensing device 1 is fed to the processor 101, and the processor 101 checks, on the basis of the timing with which the output is yielded, whether the output is image data or compensation data, and then outputs it to the succeeding stage. At this time, to permit the controller 100 to recognize whether the signal currently being fed to the succeeding stage is image data or compensation data, the processor 101 feeds the controller 100 with information on the signal it is currently outputting.

The above-described configuration and operation of the image-sensing apparatus are common to all of the descriptions to follow. Now, the solid-state image-sensing device provided in this image-sensing apparatus will be described.

First Example of the Pixel Configuration

Hereinafter, embodiments of the solid-state image-sensing device 1 provided in the image-sensing apparatus shown in Fig. 1 will be described with reference to the drawings. Fig. 2 schematically shows the configuration of part of a two-dimensional MOS-type solid-state image-sensing device employed in an image-sensing apparatus embodying the invention. In this figure, reference symbols G11 to Gmn represent pixels that are arranged in a two-dimensional array (in a matrix). Reference numeral 2 represents a vertical scanning circuit, which scans lines (rows) 4-1, 4-2, . . . , 4-n sequentially. Reference numeral 3 represents a horizontal scanning circuit, which reads out, sequentially pixel by pixel in a horizontal direction, the signals fed from the individual pixels to output signal lines 6-1, 6-2, . . . , 6-m as a result of photoelectric conversion performed in those pixels.

Reference numeral 5 represents a power line. The individual pixels are connected not only to the lines 4-1, 4-2, . . . , 4-n, to the output signal lines 6-1, 6-2, . . . , 6-m, and to the power line 5 mentioned above, but also to other lines (for example clock lines and bias supply lines). These other lines, however, are omitted in Fig. 2, and are shown in Fig. 3, which shows a first embodiment of the invention.

As shown in Fig. 2, for each of the output signal lines 6-1, 6-2, . . . , 6-m, one N-channel MOS transistor Q2 is provided. Here, a description will be given only with respect to the output signal line 6-1 as their representative. The MOS transistor Q2 has its drain connected to the output signal line 6-1, has its source connected to a signal line 9 serving as a final destination line, and has its gate connected to the horizontal scanning circuit 3. As will be described later, within each pixel, another N-channel MOS transistor (a fifth MOS transistor) T5 functioning as a switch is provided. Whereas this MOS transistor T5 serves to select a row, the MOS transistor Q2 serves to select a column.

First Embodiment

Now, a first embodiment of the invention, which is applicable to each pixel of the first example of the pixel configuration shown in Fig. 2, will be described with reference to the drawings.

In Fig. 3, a pn photodiode PD serves as a photosensitive element (photoelectric conversion element). The anode of this photodiode PD is connected to the drain of a first MOS transistor T1, also to the drain of a third MOS transistor T3, and also to the gate of a fourth MOS transistor T4. The source of the MOS transistor T4 is connected to the drain of a fifth MOS transistor T5 for selecting a

row. The source of this MOS transistor T5 is connected to the output signal line 6 (this output signal line 6 corresponds to the output signal lines 6-1, 6-2, . . . , 6-m in Fig. 2). The MOS transistors T1 to T5 are all N-channel MOS transistors, and have their back gates grounded.

5 A direct-current voltage VPD is applied to the cathode of the photodiode PD. On the other hand, a signal ϕ VPS is applied to the source of the MOS transistor T1, and also to one end of a capacitor C of which the other end is connected to the source of the MOS transistor T4. A direct-current voltage VRB is applied to the source of the MOS transistor T2, and a signal ϕ VRS is fed to the gate of the same
10 MOS transistor T2. The drain of this MOS transistor T2 is connected to the gate of the MOS transistor T1 and also to the source of the MOS transistor T3. A signal ϕ D is fed to the drain of the MOS transistor T4. Moreover, a signal ϕ SW is fed to the gate of the MOS transistor T3. Furthermore, a signal ϕ V is fed to the gate of the MOS transistor T5. It is to be noted that, in this embodiment, the signal ϕ VPS
15 is a binary signal that takes one of two predetermined levels, i.e. either a low level or a high level, at a time. Here, a low level refers to a level that causes the MOS transistor T1 to operate in a subthreshold region, and a high level is a level that is approximately equal to the direct-current voltage VPD.

In this pixel having a circuit configuration as described above, to permit the
20 MOS transistor T1 to operate in a subthreshold region, it is necessary to know the threshold value TH at the gate of the MOS transistor T1. Now, the method of detecting this threshold value TH (i.e. the method of detecting variations in sensitivity of the individual pixels) will be described with reference to Figs. 3, 4A, 4B, and 4C. Fig. 4A is a diagram showing the structure of the photodiode PD and

the MOS transistor T1. Figs. 4B and 4C are diagrams showing the potential relationship in the photodiode PD and the MOS transistor T1. In the potential diagrams of Figs. 4B and 4C, the arrow at the left indicates the direction in which the potential increases.

Incidentally, as shown in Fig. 4A, the photodiode PD is formed, for example, by forming an N-type well layer 11 in a P-type semiconductor substrate (hereinafter referred to as the "P-type substrate") 10 and then forming, in this N-type well layer 11, a P-type diffusion layer 12. On the other hand, the MOS transistor T1 is formed by forming N-type diffusion layers 13 and 14 in the P-type substrate 10 and then forming, on top of the channel left between those N-type diffusion layers 13 and 14, an oxide film 15 and, further on top thereof, a polysilicon layer 16. Here, the N-type well layer 11 functions as the cathode of the photodiode PD, and the P-type diffusion layer 12 functions as the anode thereof. On the other hand, the N-type diffusion layers 13 and 14 function as the drain and the source, respectively, of the MOS transistor T1, and the oxide film 15 and the polysilicon layer 16 function as the gate insulating film and the gate electrode, respectively, thereof. Here, in the P-type substrate 10, the region between the N-type diffusion layers 13 and 14 is called the sub-gate region.

(1) How to detect variations in sensitivity of the individual pixels

First, the voltage of the signal ϕ_{SW} is turned to a low level to turn off the MOS transistor T3, and the voltage of the signal ϕ_{VRS} is turned to a high level to turn on the MOS transistor T2. Moreover, the signal ϕ_V is turned to a low level to turn off the transistor T5. In this way, the gate of the MOS transistor T1 is

disconnected from the gate of the MOS transistor T4, and the direct-current voltage VRB is applied to the gate of the MOS transistor T1. Furthermore, the voltage of the signal ϕ_D is turned to a high level (a potential equal to or close to the direct-current voltage VPD). In this embodiment, the threshold value of a transistor is
5 detected by injecting an electric charge into it, and therefore, in detecting variations in sensitivity of the individual pixels, there is no need to illuminate the photodiodes used as photosensitive elements with light prepared specially to expose them to uniform light or the like. This applies to all of the embodiments described hereafter.

10 Next, the voltage of the signal ϕ_{VPS} fed to the source of the MOS transistor T1 is lowered. Lowering the voltage of the signal ϕ_{VPS} brings the drain, sub-gate region, and source of the MOS transistor T1 into a potential relationship as shown in Fig. 4B, causing the source, sub-gate region, and drain to have increasingly high potentials in this order. Accordingly, a negative electric charge flows into the
15 MOS transistor T1 via the source thereof. At this time, the duration for which the electric charge is accumulated is very short, and therefore the MOS transistor T1 receives practically no positive electric charge via its drain. As a result, the negative electric charge is accumulated between the drain and source of the MOS transistor T1.

20 Next, by turning the voltage of the signal ϕ_{VPS} to a potential equal to or close to the direct-current voltage VPD, as shown in Fig. 4C, the potential at the source of the MOS transistor T1 is made higher than the potential at the sub-gate region thereof. As a result, the negative electric charge accumulated between the drain and source of the MOS transistor T1 flows out to the signal line of the signal

ϕ_{VPS} . However, still the potential at the drain of the MOS transistor T1 is higher than the potential at the sub-gate region thereof, and therefore part E1 of the negative electric charge accumulated at the drain of the MOS transistor T1 remains at the drain of the MOS transistor T1. If it is assumed that the gate voltage is V_G and that the threshold voltage is V_{TH} , then the potential at the sub-gate region of the MOS transistor T1 is proportional to $(V_G - V_{TH})$. Hence, considering that the direct-current voltage V_{RB} applied to the gate of the MOS transistor T1 is constant, the amount of negative electric charge that remains at the drain thereof is proportional to $(V_{RB} - V_{TH})$.

In this way, the drain voltage of the MOS transistor T1 is proportional to the threshold voltage V_{TH} , and this drain voltage of the MOS transistor T1 appears at the gate of the MOS transistor T4. Thus, the voltage appearing at the gate of the MOS transistor T4 is proportional to the amount of negative electric charge accumulated at the drain of the MOS transistor T1, and is therefore proportional to the threshold voltage V_{TH} . This gate voltage of the MOS transistor T4 causes a current to flow through the MOS transistor T4, thereby causes an electric charge to be accumulated in the capacitor C, and thereby causes the potential at the node "a" to rise. Thus, by turning the signal ϕ_V to a high level and thereby turning on the MOS transistor T5, the electric charge accumulated in the capacitor C is fed, as an output current, to the output signal line 6. In this way, a current proportional to the threshold voltage V_{TH} of the MOS transistor T1 of one pixel after another is fed to the output signal line 6, and is acquired as compensation data to be used to correct the outputs from the individual pixels. More specifically, this current proportional to the threshold voltage V_{TH} is fed out serially, from one pixel after



another, by way of the signal line 9 so that the succeeding circuit stores it in a memory as compensation data for the individual pixels. Thus, during actual image sensing, by correcting pixel by pixel the output current from the pixels with the compensation data stored beforehand as described above, it is possible to
5 eliminate from the output signal the components resulting from variations in sensitivity of the individual pixels. A practical example of how this compensation is achieved is shown in Fig. 20 and will be described later.

After the acquisition of compensation data as described above, the MOS transistor T5 is turned off, and the signal ϕD is turned to a low level so that,
10 through the MOS transistor T4, the electric charge accumulated in the capacitor C is discharged therefrom to the signal line of the signal ϕD , and thereby the capacitor C, and thus the potential at the node "a", is initialized. Subsequently, the MOS transistor T3 is turned on so that, through the MOS transistors T2 and T3, the electric charges accumulated in the photodiode PD, at the drain of the MOS
15 transistor T1, and at the gate of the MOS transistor T4 are discharged and thereby those elements are initialized.

The detection of variations in sensitivity itself takes only a very short time, and therefore, in the process described above, the photodiode does not necessarily have to be prevented from exposure to light during the detection of variations.

20 However, it is preferable that the photodiode be prevented at least from exposure to light so intense as to affect the detection of variations in threshold values. Although it is preferable to keep the photodiode in a dark state, it suffices to keep the photodiode in ambient light as long as there is no risk of exposure to extremely intense light. This prevents the photodiode from generating an unnecessary

electric signal, and thereby makes it possible to detect variations more accurately. This applies to all of the embodiments described hereafter.

(2) How to convert the light incident on the individual pixels into an electric
5 signal

In this embodiment, by switching the voltage of the signal ϕ_{VPS} and thereby switching the bias to the MOS transistor T1, it is possible to switch between two modes of conversion so as to allow the output signal fed from each pixel to the output signal line 6 to vary either natural-logarithmically or linearly with respect to
10 the electric signal (hereafter referred to as the "photoelectric current") that the photodiode PD outputs in accordance with the amount of incident light. Here, the signal ϕ_{SW} is kept at a high level to keep the MOS transistor T3 on so that the MOS transistors T1 and T4 are kept in a state equivalent to when their gates are connected together. The two modes mentioned above will be described
15 individually below.

(2-1) Mode in which the photoelectric current is output after being converted natural-logarithmically

First, with reference to Figs. 3, 5A, and 5B, a description will be given of
20 how conversion is achieved when the signal ϕ_{VPS} is kept at a low level to permit the MOS transistors T1 and T4 to operate in a subthreshold region. In this mode, where the signal ϕ_{VRS} fed to the gate of the MOS transistor T2 is kept at a low level, the MOS transistor T2 remains off, and can thus be ignored as practically absent. In Figs. 5B and 5C, the arrow at the left indicates the direction in which the

potential increases.

When the signal ϕVPS is at a low level, the photodiode PD and the MOS transistor T1 has potentials as shown in Fig. 5B. In the circuit shown in Fig. 3, when light enters the photodiode PD, a photoelectric current is generated therein, and, due to the subthreshold characteristics of MOS transistors, a voltage having the value obtained by converting the photoelectric current natural-logarithmically appears at the gates of the MOS transistors T1 and T4. This voltage causes a current to flow through the MOS transistor T4, and, as a result, an electric charge that is equivalent to the value obtained by converting the integral of the photoelectric current natural-logarithmically is accumulated in the capacitor C. That is, a voltage proportional to the value obtained by converting the integral of the photoelectric current natural-logarithmically appears at the node "a" between the capacitor C and the source of the MOS transistor T4. Here, the MOS transistor T5 remains off.

Next, the pulse signal ϕV is fed to the gate of the MOS transistor T5 to turn this MOS transistor T5 on. This causes the electric charge accumulated in the capacitor C to be fed as the output current to the output signal line 6. This current thus fed to the output signal line 6 has the value obtained by converting the integral of the photoelectric current natural-logarithmically. In this way, it is possible to read a signal (output current) that is proportional to the logarithm of the amount of incident light. After this signal has been read, the MOS transistor T5 is turned off. Thereafter, the signal ϕD is turned to a low level, so that the electric charge accumulated in the capacitor C is discharged through the MOS transistor T4 to the signal line of the signal ϕD , and thereby the potential at the capacitor C, and



thus at the node "a", is initialized. By repeating this sequence of operations at regular time intervals, it is possible to shoot continuously an ever-changing subject image with a wide dynamic range. It is to be noted that, when the output current is so controlled as to vary natural-logarithmically with respect to the amount of
5 incident light as in this mode, the signal ϕVRS is kept at a low level all the time.

(2-2) Mode in which the photoelectric current is output after being converted linearly

Next, a description will be given of how conversion is achieved when the
10 signal ϕVPS is kept at a high level. In this mode, the photodiode PD and the MOS transistor T1 have potentials as shown in Fig. 5C. Accordingly, the MOS transistor T1 is kept practically off, and thus no current flows through the channel between the source and the drain thereof. Moreover, the signal ϕVRS fed to the gate of the MOS transistor T2 is kept at a low level, and thus this MOS transistor
15 T2 is kept off.

First, the MOS transistor T5 is turned off, and the signal ϕD is turned to a low level (to a potential lower than the signal ϕVPS), so that the electric charge in the capacitor C flows through the MOS transistor T4 to the signal line of the signal ϕD , and thereby the capacitor C is reset. As a result, the potential at the node "a"
20 is initialized, for example, to a potential lower than the direct-current voltage VPD. This potential is maintained by the capacitor C. Thereafter, the signal ϕD is turned back to a high level (to a potential equal to or close to the direct-current voltage VPD). In this state, when light enters the photodiode PD, a photoelectric current is generated therein. At this time, since capacitors exist between the back

gate and gate of the MOS transistor T1 and at the junction of the photodiode PD, the electric charge resulting from the photoelectric current is accumulated mainly at the gates of the MOS transistors T1 and T4. Thus, the gate voltage of the MOS transistors T1 and T4 has the value proportional to the integral of the photoelectric
5 current.

Now that the potential at the node "a" is lower than the direct-current voltage VPD, the MOS transistor T4 is on. As a result, a current corresponding to the gate voltage of the MOS transistor T4 flows through the MOS transistor T4 as its drain current, and thus an electric charge proportional to the gate voltage of the
10 MOS transistor T4 is accumulated in the capacitor C. Accordingly, the voltage at the node "a" has the value proportional to the integral of the photoelectric current. Next, the pulse signal ϕV is fed to the gate of the MOS transistor T5 to turn this MOS transistor T5 on, so that the electric charge accumulated in the capacitor C is fed as the output current to the output signal line 6. This output current has the
15 value obtained by converting the integral of the photoelectric current linearly.

In this way, it is possible to read a signal (output current) that is proportional to the amount of incident light. Thereafter, the MOS transistor T5 is turned off, and the signal ϕD is turned to a low level, so that the electric charge accumulated in the capacitor C is discharged through the MOS transistor T4 to the signal line of the
20 signal ϕD , and thereby the potential at the capacitor C, and thus at the node "a", is initialized. Thereafter, a high level is fed as the signal ϕVRS to the gate of the MOS transistor T2 to turn this MOS transistor T2 on so as to initialize the photodiode PD, the drain voltage of the MOS transistor T1, and the gate voltage of the MOS transistors T1 and T4. By repeating this sequence of operations at

regular time intervals, it is possible to shoot continuously an ever-changing subject image with a satisfactory S/N ratio.

As described above, in this embodiment, simple manipulation of potentials makes it possible to switch the output characteristics of a single pixel among a plurality of patterns of output characteristics. When the conversion mode is switched from logarithmic conversion to linear conversion, it is preferable to switch the output first by adjusting the potential of the signal ϕ_{VPS} and then make the MOS transistor T2 reset the MOS transistor T1 and others. On the other hand, when the conversion mode is switched from linear conversion to logarithmic conversion, it is not necessary to make the MOS transistor T2 reset the MOS transistor T1 and others. This is because the carriers accumulated in the MOS transistor T1 as a result of the MOS transistor T1 not really being kept in a completely off state are canceled by carriers of the opposite polarity.

The reading of the signal from each pixel may be achieved by means of a CCD (charge-coupled device). In that case, the transfer of an electric charge to the CCD is achieved by providing a potential barrier with a variable potential that corresponds to the MOS transistor T5 shown in Fig. 2.

Second Example of the Pixel Configuration

Fig. 6 schematically shows the configuration of part of another two-dimensional MOS-type solid-state image-sensing device employed in an image-sensing apparatus embodying the invention. In this figure, reference symbols G11 to Gmn represent pixels that are arranged in a two-dimensional array (in a matrix). Reference numeral 2 represents a vertical scanning circuit, which scans lines

(rows) 4-1, 4-2, . . . , 4-n sequentially. Reference numeral 3 represents a horizontal scanning circuit, which reads out, sequentially pixel by pixel in a horizontal direction, the signals fed from the individual pixels to output signal lines 6-1, 6-2, . . . , 6-m as a result of photoelectric conversion performed in those pixels.

5 Reference numeral 5 represents a power line. The individual pixels are connected not only to the lines 4-1, 4-2, . . . , 4-n, to the output signal lines 6-1, 6-2, . . . , 6-m, and to the power line 5 mentioned above, but also to other lines (for example clock lines and bias supply lines). These other lines, however, are omitted in Fig. 6, and are shown in individual embodiments of the invention shown in Fig. 8 and the
10 following figures.

As shown in Fig. 6, for each of the output signal lines 6-1, 6-2, . . . , 6-m, a pair of N-channel MOS transistors Q1 and Q2 is provided. Here, a description will be given only with respect to the output signal line 6-1 as their representative. The MOS transistor Q1 has its gate connected to a direct-current voltage line 7, has
15 its drain connected to the output signal line 6-1, and has its source connected to a direct-current voltage VPSA line 8. On the other hand, the MOS transistor Q2 has its drain connected to the output signal line 6-1, has its source connected to a signal line 9 serving as a final destination line, and has its gate connected to the horizontal scanning circuit 3.

20 As will be described later, the pixels G11 to Gmn are each provided with an N-channel MOS transistor Ta that outputs a signal in accordance with the photoelectric charge generated in each pixel. How this MOS transistor Ta is connected to the above-mentioned MOS transistor Q1 is shown in Fig. 7A. This MOS transistor Ta corresponds to a sixth MOS transistor T6 in the second and

third embodiments, and corresponds to a fourth MOS transistor T4 in the fourth and fifth embodiments. Here, the direct-current voltage VPDA connected to the source of the MOS transistor Q1 and the direct-current voltage VPDA connected to the drain of the MOS transistor Ta fulfill the relation $VPDA > VPDA$, where the
5 direct-current voltage VPDA is equal to, for example, the ground-level voltage. In this circuit configuration, the signal from a pixel is fed to the gate of the upper-stage MOS transistor Ta, and a direct-current voltage DC is kept applied to the gate of the lower-stage MOS transistor Q1. Thus, the lower-stage MOS transistor Q1 is equivalent to a resistor or constant-current source, and therefore the circuit shown
10 in Fig. 7A forms an amplifier circuit of a source-follower type. Here, it can safely be assumed that, as a result of amplification, the MOS transistor Ta outputs a current.

The MOS transistor Q2 is controlled by the horizontal scanning circuit 3 so as to function as a switching device. As will be described later, in all of the
15 embodiments of the invention shown in Fig. 8 and the following figures, within each pixel, another, i.e. a fifth, N-channel MOS transistor T5 functioning as a switch is provided. If this fifth MOS transistor T5 is illustrated explicitly, the circuit shown in Fig. 7A has, more precisely, a circuit configuration as shown in Fig. 7B. Specifically, the MOS transistor T5 is inserted between the MOS
20 transistor Q1 and the MOS transistor Ta. Here, the MOS transistor T5 serves to select a row, and the MOS transistor Q2 serves to select a column. It is to be noted that the circuit configurations shown in Figs. 6, 7A, and 7B are common to the second to fifth embodiments of the invention described hereafter.

The circuit configuration shown in Figs. 7A and 7B permits the signal to be

output with a high gain. Accordingly, even in a case where the photoelectric current generated in a photosensitive element is converted natural-logarithmically to obtain a wider dynamic range and thus the output signal obtained is comparatively low, this amplifier circuit amplifies the signal so as to make it sufficiently high and thus easier to process in the succeeding signal processing circuit (not shown). Here, the MOS transistor Q1 that serves as the load resistor of the amplifier circuit is provided within each pixel; however, such transistors may be provided, instead, one for each of the output signal lines 6-1, 6-2, . . . , 6-m, i.e. one for each of the groups of pixels that individually constitute columns, with the pixels constituting each column collectively connected to one of the output signal lines 6-1, 6-2, . . . , 6-m. This helps reduce the number of load resistors or constant-current sources required, and thus reduce the area occupied by the amplifying circuits on a semiconductor chip.

Second Embodiment

Next, a second embodiment of the invention, which is applicable to each pixel of the second example of the pixel configuration shown in Fig. 6, will be described with reference to the drawings. Fig. 8 is a circuit diagram showing the configuration of each pixel of the solid-state image-sensing device of this embodiment. It is to be noted that such elements, signal lines, and others as are used for the same purposes here as in the pixel shown in Fig. 2 are identified with the same reference symbols, and their detailed descriptions will be omitted.

As shown in Fig. 8, in this embodiment, as compared with the pixel shown in Fig. 2, there are provided additionally a sixth MOS transistor T6 having its gate

connected to the node "a" for performing current amplification in accordance with the voltage at the node "a", a fifth MOS transistor T5 having its drain connected to the source of the MOS transistor T6 for row selection, a seventh MOS transistor T7 having its drain connected to the node "a" for initializing the potential at the capacitor C, and thus at the node "a". The source of the MOS transistor T5 is connected to the output signal line 6 (this output signal line 6 corresponds to the output signal lines 6-1, 6-2, . . . 6-m shown in Fig. 6). Just like the MOS transistors T1 to T5, the MOS transistors T6 and T7 are all N-channel MOS transistors, and have their back gates grounded.

A direct-current voltage VPD is applied to the drain of the MOS transistor T6, and a signal ϕV is fed to the gate of the MOS transistor T5. A direct-current voltage VRB2 is applied to the source of the MOS transistor T7, and a signal $\phi VRS2$ is fed to the gate of the same MOS transistor T7. The direct-current voltage VPD is applied also to the drain of the MOS transistor T4. In this embodiment, it is possible to make the MOS transistors T1 to T5 and the capacitor C to operate in the same manner as in the first embodiment (Fig. 3) so as to output a current that permits the detection of variations in sensitivity of the individual pixels. Now, how this is achieved will be described.

(1) How to detect variations in sensitivity of the individual pixels

First, the MOS transistor T5 is turned off, and the MOS transistor T3 is turned off to bring the MOS transistors T1 and T4 into a state equivalent to when their gates are disconnected from each other. In addition, the MOS transistor T2 is turned on to apply the direct-current voltage VRB to the gate of the MOS

transistor T1. Furthermore, the voltage of the signal ϕ_{VRS2} is turned to a low level to turn off the MOS transistor T7. With the individual pixels brought into this state, the voltage of the signal ϕ_{VPS} applied to the source of the MOS transistor T1 is turned first to a low level and then back to a high level as in the first embodiment (Figs. 4B and 4C). This causes a negative electric charge to be accumulated at the drain of the MOS transistor T1, and, in accordance with the drain voltage thereof that varies with this negative electric charge, a current flows through the MOS transistor T4.

This current flowing through the MOS transistor T4 causes an electric charge to be accumulated in the capacitor C, and thereby causes the potential at the node "a" to rise. Next, the signal ϕ_V is turned to a high level to turn on the MOS transistor T5. This causes a current to flow through the MOS transistor T6 in accordance with the voltage appearing at the node "a", and this current is fed, as the output current, to the output signal line 6. The output current thus fed to the output signal line 6 is proportional to the threshold voltage V_{TH} of the MOS transistor T1, and therefore, on the basis of this output current, it is possible to acquire compensation data to be used to correct the outputs from the individual pixels. Moreover, as in the first embodiment (Fig. 3), this current proportional to the threshold voltage V_{TH} is fed out serially, from one pixel after another, by way of the signal line 9 shown in Fig. 6 so that the succeeding circuit stores it in a memory as compensation data for the individual pixels. Thus, during actual image sensing, by using the compensation data thus stored, it is possible to eliminate from the output signal the components resulting from variations in sensitivity of the individual pixels. A practical example of how this compensation

is achieved is shown in Fig. 20 and will be described later.

After the acquisition of compensation data as described above, the MOS transistor T5 is turned off, and a high level is fed as the signal $\phi VRS2$ to the gate of the MOS transistor T7 so that the MOS transistor T7 is turned on and thereby the capacitor C, and thus the potential at the node "a", is initialized. Subsequently, the MOS transistor T3 is turned on so that, through the MOS transistors T2 and T3, the electric charges accumulated in the photodiode PD, at the drain of the MOS transistor T1, and at the gate of the MOS transistor T4 are discharged and thereby those elements are initialized.

(2) How to convert the light incident on the individual pixels into an electric signal

In this embodiment, by switching the voltage of the signal ϕVPS and thereby switching the bias to the MOS transistor T1, it is possible, as in the first embodiment, to switch between two modes of conversion so as to allow the output signal fed from each pixel to the output signal line 6 to vary either natural-logarithmically or linearly with respect to the photoelectric current that the photodiode PD outputs in accordance with the amount of incident light. Here, the signal ϕSW is kept at a high level to keep the MOS transistor T3 on so that the MOS transistors T1 and T4 are kept in a state equivalent to when their gates are connected together. The two modes mentioned above will be described individually below.

(2-1) Mode in which the photoelectric current is output after being converted

natural-logarithmically

First, a description will be given of how conversion is achieved when the signal ϕ_{VPS} is kept at a low level to permit the MOS transistors T1 and T4 to operate in a subthreshold region. As in the first embodiment, in this mode, where
5 the signal ϕ_{VRS} fed to the gate of the MOS transistor T2 is kept at a low level, the MOS transistor T2 remains off, and can thus be ignored as practically absent.

When light enters the photodiode PD, a photoelectric current is generated therein, and, due to the subthreshold characteristics of MOS transistors, a voltage having the value obtained by converting the photoelectric current natural-
10 logarithmically appears at the gates of the MOS transistors T1 and T4. This voltage causes a current to flow through the MOS transistor T4, and, as a result, an electric charge that is equivalent to the value obtained by converting the integral of the photoelectric current natural-logarithmically is accumulated in the capacitor C. That is, a voltage proportional to the value obtained by converting the integral of
15 the photoelectric current natural-logarithmically appears at the node "a" between the capacitor C and the source of the MOS transistor T4. Here, the MOS transistors T5 and T7 remain off.

Next, the pulse signal ϕ_V is fed to the gate of the MOS transistor T5 to turn this MOS transistor T5 on. This causes a current proportional to the voltage
20 applied to the gate of the MOS transistor T6 to flow through the MOS transistors T5 and T6 to the output signal line 6. Now, the voltage applied to the gate of the MOS transistor T6 is equal to the voltage applied to the node "a", and therefore the current thus fed to the output signal line 6 has the value obtained by converting the integral of the photoelectric current natural-logarithmically.

In this way, it is possible to read a signal (output current) that is proportional to the logarithm of the amount of incident light. After this signal has been read, the MOS transistor T5 is turned off, and a high level is fed as the signal $\phi VRS2$ to the gate of the MOS transistor T7, so that the MOS transistor T7 is turned on, and thereby the potential at the capacitor C, and thus at the node "a", is initialized. It is to be noted that, when the output current is so controlled as to vary natural-logarithmically with respect to the amount of incident light as in this mode, the signal ϕVRS is kept at a low level all the time.

(2-2) Mode in which the photoelectric current is output after being converted linearly

Next, a description will be given of how conversion is achieved when the signal ϕVPS is kept at a high level. First, a low level is fed as the signal ϕVRS to the gate of the MOS transistor T2 to turn this MOS transistor T2 practically off. In addition, a high level is fed as the signal $\phi VRS2$ to the gate of the MOS transistor T7 to turn this MOS transistor T7 on and thereby reset the capacitor C, and simultaneously the potential at the node "a" is initialized to the potential $VRB2$, which is lower than the direct-current voltage VPD . This potential is maintained by the capacitor C. Thereafter, the signal $\phi VRS2$ is turned to a low level to turn the MOS transistor T7 off. In this state, when light enters the photodiode PD, a photoelectric current is generated therein. At this time, since capacitors exist between the back gate and gate of the MOS transistor T1 and at the junction of the photodiode PD, the electric charge resulting from the photoelectric current is accumulated mainly at the gates of the MOS transistors T1 and T4. Thus, the gate

voltage of the MOS transistors T1 and T4 has the value proportional to the integral of the photoelectric current.

Now that the potential at the node "a" is lower than the direct-current voltage VPD, the MOS transistor T4 is on. As a result, a current corresponding to the gate voltage of the MOS transistor T4 flows through the MOS transistor T4 as its drain current, and thus an electric charge proportional to the gate voltage of the MOS transistor T4 is accumulated in the capacitor C. Accordingly, the voltage at the node "a" has the value proportional to the integral of the photoelectric current.

Next, the pulse signal ϕV is fed to the gate of the MOS transistor T5 to turn this MOS transistor T5 on, so that a current proportional to the voltage applied to the gate of the MOS transistor T6 flows through the MOS transistors T5 and T6 to the output signal line 6. Since the voltage applied to the gate of the MOS transistor T6 is equal to the voltage at the node "a", the current thus fed to the output signal line 6 has the value obtained by converting the integral of the photoelectric current linearly.

In this way, it is possible to read a signal (output current) that is proportional to the amount of incident light. After this signal has been read, the MOS transistor T5 is turned off, and a high level is fed as the signal ϕVRS to the gate of the MOS transistor T2 to turn this MOS transistor T2 on so as to initialize the photodiode PD, the drain of the MOS transistor T1, and the gates of the MOS transistors T1 and T4. Next, a high level is fed as the signal $\phi VRS2$ to the gate of the MOS transistor T7 to turn this MOS transistor T7 on and thereby initialize the potential at the capacitor C, and thus at the node "a".

Third Embodiment

Next, a third embodiment of the invention will be described with reference to the drawings. Fig. 9 is a circuit diagram showing the configuration of each pixel of the solid-state image-sensing device of this embodiment. It is to be noted that such elements, signal lines, and others as are used for the same purposes here as in the pixel shown in Fig. 8 are identified with the same reference symbols, and their detailed descriptions will be omitted.

As shown in Fig. 9, in this embodiment, the initialization of the potential at the capacitor C, and thus at the node "a", is achieved by feeding the signal ϕD to the drain of the MOS transistor T4, and thus the MOS transistor T7 found in the previous embodiment is omitted. In other respects, each pixel of this embodiment is configured in the same manner as in the second embodiment (Fig. 8). Here, while the signal ϕD is kept at a high level, the capacitor C performs integration; while the signal ϕD is kept at a low level, the electric charge accumulated in the capacitor C is discharged through the MOS transistor T4 to make the voltage at the capacitor C, and thus at the gate of the MOS transistor T6, approximately equal to the low-level voltage of the signal ϕD (that is, the voltage is reset). In this embodiment, the omission of the MOS transistor T7 helps simplify the circuit configuration.

In this embodiment, compensation data of the pixel is acquired in the following manner. The MOS transistor T3 is turned off to bring the MOS transistors T1 and T4 into a state equivalent to when their gates are disconnected from each other. In addition, the MOS transistor T2 is turned on to apply the direct-current voltage VRB to the gate of the MOS transistor T1. Furthermore, the

signal ϕD is turned to a high level (for example, to a voltage approximately equal to the direct-current voltage VPD), and, as in the first embodiment (Figs. 4B and 4C), the voltage of the signal ϕVPS is turned first to a low level and then back to a high level so that a negative electric charge is accumulated at the drain of the MOS transistor T1. In accordance with the drain voltage of the MOS transistor T1 that varies with this negative electric charge, a current flows through the MOS transistor T4, causing an electric charge to be accumulated in the capacitor C and thus causing the potential at the node "a" to rise.

Then, with predetermined timing, the MOS transistor T5 is turned on so that a current proportional to the voltage applied to the gate of the MOS transistor T6 in accordance with the voltage appearing at the node "a" is fed to the output signal line 6. The output current thus fed to the output signal line 6 is proportional to the threshold voltage V_{TH} of the MOS transistor T1, and therefore, on the basis of this output current, it is possible to acquire compensation data to be used to correct the outputs from the individual pixels. Moreover, as in the second embodiment, this current proportional to the threshold voltage V_{TH} is fed out serially, from one pixel after another, by way of the signal line 9 shown in Fig. 6 so that the succeeding circuit stores it in a memory as compensation data for the individual pixels. Thus, during actual image sensing, by using the compensation data thus stored, it is possible to eliminate from the output signal the components resulting from variations in sensitivity of the individual pixels. A practical example of how this compensation is achieved is shown in Fig. 20 and will be described later.

Thereafter, the MOS transistor T5 is turned off, and the signal ϕD is turned to a low level (a voltage lower than the signal ϕVPS) so that, through the MOS

transistor T4, the electric charge in the capacitor C is discharged therefrom to the signal line of the signal ϕD and thereby the potential at the capacitor C, and thus at the node "a", is initialized. Subsequently, the MOS transistor T3 is turned on so that, through the MOS transistors T2 and T3, the electric charges accumulated in the photodiode PD, at the drain of the MOS transistor T1, and at the gate of the MOS transistor T4 are discharged and thereby those elements are initialized.

On the other hand, image sensing is performed in the following manner. In a case where the output current is produced by converting the photoelectric current natural-logarithmically, the MOS transistor T3 is kept on, and the MOS transistor T2 is kept off. Moreover, the signal ϕVPS is turned to a low level, and the signal ϕD is turned to a high level so that an electric charge equivalent to the value obtained by converting the integral of the photoelectric current natural-logarithmically is accumulated in the capacitor C. Then, with predetermined timing, the MOS transistor T5 is turned on so that a current proportional to the voltage applied to the gate of the MOS transistor T6 is fed through the MOS transistors T5 and T6 to the output signal line 6.

Thereafter, the MOS transistor T5 is turned off, and the signal ϕD is turned to a low level. As a result, the electric charge accumulated in the capacitor C flows through the MOS transistor T4 to the signal line of the signal ϕD , and thereby the voltage at the capacitor C, and thus at the node "a", is initialized.

By contrast, in a case where the output current is produced by converting the photoelectric current linearly, first, the MOS transistor T3 is kept on, and the MOS transistor T2 is turned off. Moreover, the signal ϕVPS and the signal ϕD are turned to a high level. Then, an initialization operation is performed using the

MOS transistor T4 so as to turn the voltage at the node "a" to a voltage lower than the direct-current voltage VPD as in the second embodiment. In this state, an electric charge equivalent to the value obtained by converting the integral of the photoelectric current linearly is accumulated in the capacitor C. Then, with
5 predetermined timing, the MOS transistor T5 is turned on so that a current proportional to the voltage applied to the gate of the MOS transistor T6 is fed through the MOS transistors T5 and T6 to the output signal line 6.

Thereafter, first, the MOS transistor T2 is turned on so as to initialize the photodiode PD, the drain of the MOS transistor T1, and the gates of the MOS
10 transistors T1 and T4. Subsequently, the signal ϕD is turned to a low level so that the electric charge accumulated in the capacitor C is discharged through the MOS transistor T4 to the signal line of the signal ϕD , and thereby the voltage at the node "a" is initialized to a voltage lower than the signal ϕVPS .

15 **Fourth Embodiment**

Next, a fourth embodiment of the invention will be described with reference to the drawings. Fig. 10 is a circuit diagram showing the configuration of each pixel of the solid-state image-sensing device of this embodiment. It is to be noted that such elements, signal lines, and others as are used for the same purposes here
20 as in the pixel shown in Fig. 9 are identified with the same reference symbols, and their detailed descriptions will be omitted.

As shown in Fig. 10, in this embodiment, the direct-current voltage VPD is applied to the drain of the MOS transistor T4, and the capacitor C and the MOS transistor T6 found in the previous embodiment are omitted. That is, the MOS

transistor T4 has its source connected to the drain of the MOS transistor T5, and receives at its drain the direct-current voltage VPD. In other respects, each pixel of this embodiment is configured in the same manner as in the third embodiment (Fig. 9).

5 In this pixel having a circuit configuration as described above, compensation data is acquired in the following manner. As in the third embodiment, the MOS transistor T2 is kept on and the MOS transistor T3 is kept off so that the MOS transistors T1 and T4 are kept in a state equivalent to when their gates are disconnected from each other. In addition, the direct-current voltage VRB is
10 applied to the gate of the MOS transistor T1. Moreover, as in the first embodiment (Figs. 4B and 4C), the voltage of the signal ϕ_{VPS} is turned first to a low level and then back to a high level so that a negative electric charge is accumulated at the drain of the MOS transistor T1. In accordance with the drain voltage of the MOS transistor T1 that varies with this negative electric charge, a current flows through
15 the MOS transistor T4.

Then, with predetermined timing, the MOS transistor T5 is turned on so that a current proportional to the voltage applied to the gate of the MOS transistor T4 is fed to the output signal line 6. The output current thus fed to the output signal line 6 is proportional to the threshold voltage V_{TH} of the MOS transistor T1, and
20 therefore, on the basis of this output current, it is possible to acquire compensation data to be used to correct the outputs from the individual pixels. Moreover, as in the third embodiment, this current proportional to the threshold voltage V_{TH} is fed out serially, from one pixel after another, by way of the signal line 9 shown in Fig. 6 so that the succeeding circuit stores it in a memory as compensation data for the

individual pixels. Thus, during actual image sensing, by using the compensation data thus stored, it is possible to eliminate from the output signal the components resulting from variations in sensitivity of the individual pixels. A practical example of how this compensation is achieved is shown in Fig. 20 and will be
5 described later.

After the acquisition of compensation data as described above, first, the MOS transistor T5 is turned off, and then the MOS transistor T3 is turned on. As a result, through the MOS transistors T2 and T3, the electric charges accumulated in the photodiode PD, at the drain of the MOS transistor T1, and at the gate of the
10 MOS transistor T4 are discharged and thereby those elements are initialized.

In the pixel shown in Fig. 10, as in the third embodiment, by keeping the MOS transistor T3 on and switching the voltage of the signal ϕVPS so as to switch the bias to the MOS transistor T1, it is possible to switch between two modes of conversion so as to allow the output signal fed to the output signal line 6 to vary
15 either natural-logarithmically or linearly with respect to the photoelectric current.

As a result of the voltage of the signal ϕVPS being switched in such a way that the gate voltage of the MOS transistor T4 varies either natural-logarithmically or linearly with respect to the photoelectric current generated in the photodiode PD, a current having the value proportional either natural-logarithmically or linearly to
20 the photoelectric current flows through the MOS transistor T4 as its drain current. Then, when the signal ϕV is fed to the gate of the MOS transistor T5 to turn this MOS transistor T5 on, a current having the value proportional either natural-logarithmically or linearly to the photoelectric current flows through the MOS transistor T5 as its drain current to the output signal line 6. At this time, the drain

voltage of the MOS transistor Q1 (Fig. 6), which is determined by the on-state resistances of the MOS transistors T4 and Q1 and the current flowing therethrough, appears as the output signal on the output signal line 6. After the signal has been read in this way, the MOS transistor T5 is turned off. In a case where the signal thus read is proportional linearly to the amount of incident light, after the signal has been read, the MOS transistor T2 is turned on so as to initialize the photodiode PD, the drain of the MOS transistor T1, and the gates of the MOS transistors T1 and T4.

In this embodiment, it is not necessary to perform integration of the photoelectric signal by the use of a capacitor C as performed in the third embodiment described above, and thus no time is required for such integration, nor is it necessary to reset the capacitor C. This ensures accordingly faster signal processing. Moreover, as compared with the third embodiment, the capacitor C and the MOS transistor T6 can be omitted, and this helps further simplify the circuit configuration and reduce the pixel size.

Fifth Embodiment

Next, a fifth embodiment of the invention will be described with reference to the drawings. Fig. 11 is a circuit diagram showing the configuration of each pixel of the solid-state image-sensing device of this embodiment. It is to be noted that such elements, signal lines, and others as are used for the same purposes here as in the pixel shown in Fig. 10 are identified with the same reference symbols, and their detailed descriptions will be omitted.

As shown in Fig. 11, in this embodiment, the signal ϕ_{VPD} is fed to the

cathode of the photodiode PD, a direct-current voltage VPS is applied to the source of the MOS transistor T1, and a direct-current voltage VDD is applied to the drain of the MOS transistor T4. In other respects, each pixel of this embodiment is configured in the same manner as in the fourth embodiment (Fig. 10).

5 In this pixel having a circuit configuration as described above, compensation data is acquired in the following manner. As in the fourth embodiment, the MOS transistor T2 is kept on and the MOS transistor T3 is kept off so that the MOS transistors T1 and T4 are kept in a state equivalent to when their gates are disconnected from each other. In addition, the direct-current voltage VRB is
10 applied to the gate of the MOS transistor T1.

Then, the voltage of the signal ϕ_{VPD} is increased so as to bring the drain, sub-gate region, and source of the MOS transistor T1 into a potential relationship as shown in Fig. 4B. This causes a negative electric charge to be accumulated between the drain and source of the MOS transistor T1. Thereafter, the voltage of
15 the signal ϕ_{VPD} is lowered to make the MOS transistor T1 have a potential relationship as shown in Fig. 4C. As a result, the electric charge accumulated at the sub-gate region and source of the MOS transistor T1 is discharged, and thus an electric charge remains accumulated only at the drain of the MOS transistor 1. In accordance with the drain voltage of the MOS transistor 1 that varies with this
20 negative electric charge, a current flows through the MOS transistor T4.

Then, as in the fourth embodiment, with predetermined timing, the MOS transistor T5 is turned on so that a current proportional to the voltage applied to the gate of the MOS transistor T4 is fed to the output signal line 6. The output current thus fed to the output signal line 6 is proportional to the threshold voltage

V_{TH} of the MOS transistor T1, and therefore, on the basis of this output current, it is possible to acquire compensation data to be used to correct the outputs from the individual pixels. Moreover, as in the fourth embodiment, this current proportional to the threshold voltage V_{TH} is fed out serially, from one pixel after another, by way of the signal line 9 shown in Fig. 6 so that the succeeding circuit stores it in a memory as compensation data for the individual pixels. Thus, during actual image sensing, by using the compensation data thus stored, it is possible to eliminate from the output signal the components resulting from variations in sensitivity of the individual pixels. A practical example of how this compensation is achieved is shown in Fig. 20 and will be described later.

After the acquisition of compensation data as described above, first, the MOS transistor T5 is turned off, and then the MOS transistor T3 is turned on. As a result, through the MOS transistors T2 and T3, the electric charges accumulated in the photodiode PD, at the drain of the MOS transistor T1, and at the gate of the MOS transistor T4 are discharged and thereby those elements are initialized.

In the pixel shown in Fig. 11, image sensing is performed in the following manner. The MOS transistor T3 is kept on, and the signal ϕ_{VPD} fed to the cathode of the photodiode PD is turned to a level higher than the direct-current voltage VPS so as to permit the MOS transistors T1 and T4 to operate in a threshold region. In this state, when the MOS transistor T5 is turned on, it is possible to read a signal (output current) that is proportional to the logarithm of the amount of incident light. On the other hand, when the signal ϕ_{VPD} fed to the cathode of the photodiode PD is turned to a level as low as the direct-current voltage VPS and then the MOS transistor T5 is turned on, it is possible to read a signal proportional

to the amount of incident light.

Thus, this embodiment is different from the fourth embodiment simply in that, here, the signal ϕVPD and the direct-current voltage $V\text{PS}$ are used in place of the direct-current voltage $V\text{PD}$ and the signal ϕVPS , respectively, used in the fourth
5 embodiment. Accordingly, to switch between two modes of conversion so as to allow the output signal to vary either natural-logarithmically or linearly with respect to the amount of incident light as described above, the level of the signal ϕVPD is switched in this embodiment instead of switching the level of the signal ϕVPS as in the fourth embodiment. In other respects, the circuit of this
10 embodiment operates in the same manner as that of the fourth embodiment.

In all of the first to fifth embodiments described thus far, the MOS transistors T1 to T7 provided within each pixel as active elements are all composed of N-channel MOS transistors; however, these MOS transistors T1 to T7 may be
15 composed of P-channel MOS transistors instead. Figs. 13 and 16 to 19 show sixth to tenth embodiments, which are examples of modified versions of the first to fifth embodiments described above in which P-channel MOS are used. Accordingly, in Figs. 12 to 19, all the elements used and the voltages applied have the opposite polarities. For example, in Fig. 13 (the sixth embodiment), the direct-current
20 voltage $V\text{PD}$ is connected to the anode of the photodiode PD, and the cathode thereof is connected to the drain of the first MOS transistor T1 and to the gate of the fourth MOS transistor T4. The signal ϕVPS is fed to the source of the first MOS transistor T1.

When logarithmic conversion is performed in a pixel as shown in Fig. 13,

the voltage of the signal ϕ_{VPS} and the direct-current voltage V_{PD} fulfill the relation $\phi_{VPS} > V_{PD}$, thus an inverted relation as compared with the case shown in Fig. 3 (the first embodiment). Moreover, the output voltage of the capacitor C is initially high, and drops as a result of integration. Moreover, when the second, third, or fifth MOS transistor T2, T3, or T5 is turned on, a low voltage is applied to the gate thereof. Furthermore, in the embodiment shown in Fig. 16 (the seventh embodiment), when the seventh MOS transistor T7 is turned on, a low voltage is applied to the gate thereof. As described above, in cases where P-channel MOS transistors are used, although how the voltages are applied and the elements are connected differs partially, the circuits are configured substantially in the same manner and operate basically in the same manner. Therefore, with respect to the sixth to tenth embodiments, only illustrations are given in Figs. 13 and 16 to 19, and no descriptions will be given of their configuration and operation.

Fig. 12 is a block circuit configuration diagram illustrating the overall configuration of a solid-state image-sensing device 1 having pixels configured according to the sixth embodiment, and Fig. 14 is a block circuit configuration diagram illustrating the overall configuration of a solid-state image-sensing device 1 having pixels configured according to one of the seventh to tenth embodiments. As to Figs. 12 and 14, such elements as are found also (i.e. as play the same roles as) in Figs. 2 and 6 are identified with the same reference symbols, and their descriptions will be omitted. Here, a brief description will be given of the configuration shown in Fig. 14. A P-channel MOS transistor Q1 and a P-channel MOS transistor Q2 are connected to each of output signal lines 6-1, 6-2, . . . , 6-m that are laid in the column direction. The MOS transistor Q1 has its gate

connected to a direct-current voltage line 7, has its drain connected to the output signal line 6-1, and has its source connected to a direct-current voltage VPSA line 8. On the other hand, the MOS transistor Q2 has its drain connected to the output signal line 6-1, has its source connected to a signal line 9 serving as a final destination line, and has its gate connected to a horizontal scanning circuit 3. Here, the MOS transistor Q1, together with a P-channel MOS transistor Ta provided within each pixel, constitutes an amplifier circuit as shown in Fig. 15A. This MOS transistor Ta corresponds to the sixth MOS transistor T6 in the seventh and eighth embodiments, and corresponds to the fourth MOS transistor T4 in the ninth and tenth embodiments.

Here, the MOS transistor Q1 serves as a load resistor or constant-current source for the MOS transistor Ta. Accordingly, the direct-current voltage VPSA connected to the source of this MOS transistor Q1 and the direct-current voltage VPDA connected to the drain of the MOS transistor Ta fulfill the relation $VPDA < VPSA$, where the direct-current voltage VPDA is equal to, for example, the ground-level voltage. The MOS transistor Q1 has its drain connected to the MOS transistor Ta, and receives a direct-current voltage at its gate. The P-channel MOS transistor Q2 is controlled by the horizontal scanning circuit 3 so as to feed the output of the amplifier circuit to the signal line 9 that serves as the final destination line. If the fifth MOS transistor T5 provided within each pixel is explicitly illustrated, the circuit shown in Fig. 15A has a circuit configuration as shown in Fig. 15B.

How to Correct Image Data with Pixels of the First to Tenth Embodiments

Now, with reference to the drawings, an embodiment of the invention will be described in which an image-sensing apparatus incorporating a solid-state image-sensing device having pixels configured according to one of the first to tenth embodiments described above is applied to an image input apparatus such as a digital camera.

The image input apparatus shown in Fig. 20 includes the following components. An objective lens 51 introduces the light from a subject into the image input apparatus. An image-sensing apparatus 52 outputs an electric signal in accordance with the amount of light introduced through the objective lens 51.

A memory 53 receives the electric signal (hereafter referred to as the "image data") from the image-sensing apparatus 52 and stores it temporarily during image sensing. Another memory 54 stores compensation data. A compensation circuit 55 corrects the image data stored in the memory 53 in accordance with the compensation data stored in the memory 54 by performing predetermined compensation calculation. A signal processor 56 performs predetermined processing on the image data corrected in accordance with the compensation data by the compensation circuit 55 and feeds out the processed image data. Here, the image-sensing apparatus 52 is provided with a solid-state image-sensing device like that of the first example (Figs. 2 and 12) having pixels configured as in the first or sixth embodiments (Fig. 3 or 13), or a solid-state image-sensing device like that of the second example (Figs. 6 and 14) having pixels configured as in one of the second to fifth and seventh to tenth embodiments (Figs. 8 to 11 and 16 to 19).

This image input apparatus configured as described above operates as follows. First, immediately before the start of image sensing, for example, a

shutter (not shown) is closed so that the image-sensing apparatus 52 is brought into a dark state in which no light is introduced from the outside into it through the objective lens 51. In this dark state, compensation data is acquired from the individual pixels in the manner described in connection with each embodiment,
5 and is stored in the memory 54. In this memory 54, the compensation data is stored pixel by pixel.

After the compensation data of all the pixels of the image-sensing apparatus 52 has been stored in the memory 54, the shutter is released to start image sensing. When image sensing is started, image data is fed, pixel by pixel, from the image-sensing apparatus 52 to the memory 53. The image data is stored temporarily in
10 the memory 53, and is then fed, pixel by pixel, to the compensation circuit 55. At this time, also the compensation data is simultaneously fed from the memory 54 to the compensation circuit 55. The compensation circuit 55 corrects the image data fed thereto in accordance with the compensation data fed thereto by performing
15 predetermined compensation calculation between the image data and compensation data of corresponding pixels. The image data thus corrected is fed to the signal processor 56, which performs predetermined processing on this image data and then feeds it out. As the memories 53 and 54, there is no need to use frame memories, and it suffices to use line memories. This makes incorporation of
20 these memories into the solid-state image-sensing device easy. In this image input apparatus, it is also possible to omit the memory 53 and feed the image data output from the image-sensing apparatus 52 directly to the compensation circuit 55.

As described above, according to the present invention, it is possible to realize an image-sensing apparatus that permits detection of variations in

sensitivity of individual pixels under ambient light. This eliminates the need to illuminate the pixels with uniform light as in a conventional image-sensing apparatus to acquire compensation data used to correct the outputs from the individual pixels during actual shooting of a subject. Moreover, it is possible to

5 freely choose whether to produce an output by converting the electric signal generated in photoelectric conversion devices such as photodiodes logarithmically or linearly. Accordingly, it is possible to make the image-sensing apparatus perform logarithmic conversion when a subject having a wide brightness range is shot and make it perform linear conversion when a dimly-lit subject or a subject

10 having a narrow brightness range is shot. Thus, it is possible to shoot subjects of varying brightness, i.e. from dimly-lit to brightly-lit subjects, with high accuracy. Moreover, active elements can be composed of MOS transistors. This makes high-density integration possible, and thus makes it possible to form them on a single chip together with peripheral processing circuits such as A/D converters, digital

15 system processors, and memories.

What is claimed is:

1. An image-sensing apparatus comprising:

a plurality of pixels, the pixels each comprising:

a photoelectric conversion portion that has a photosensitive element

5 for producing an electric signal in accordance with amount of incident light and
that outputs a signal obtained by converting the electric signal natural-
logarithmically; and

a lead-out path by way of which the signal output from the
photoelectric conversion portion is fed to an output signal line; and

10 a controller that detects a variation in sensitivity of the photoelectric
conversion portion of each pixel by injecting an electric charge into the
photoelectric conversion portion.

2. An image-sensing apparatus as claimed in claim 1,

15 wherein the pixels are arranged in a matrix.

3. An image-sensing apparatus as claimed in claim 1,

wherein the pixels each further comprise an integrator circuit that integrates
the signal output from the photoelectric conversion portion so that a signal
20 integrated by the integrator circuit is fed by way of the lead-out path to the output
signal line.

4. An image-sensing apparatus as claimed in claim 3,

wherein the pixels each further comprise a resetting portion, and

wherein, after each pixel outputs the signal integrated by the integrator circuit to the output signal line, the controller makes the resetting portion discharge an electric charge from the integrator circuit.

5 5. An image-sensing apparatus as claimed in claim 4,

wherein the resetting portion comprises a transistor having a first electrode connected to the integrator circuit, a second electrode, and a control electrode, and

wherein the controller achieves discharging of the electric charge from the integrator circuit by varying a voltage applied to the control electrode of the

10 transistor so that the transistor is brought into a conducting state.

6. An image-sensing apparatus as claimed in claim 1,

wherein the pixels each further comprise an amplifying transistor that amplifies the signal output from the photoelectric conversion portion so that a
15 signal output from the amplifying transistor is fed by way of the lead-out path to the output signal line.

7. An image-sensing apparatus as claimed in claim 6, further comprising:

20 load resistors or constant-current sources connected to the output signal line, a total number of the load resistors or constant-current sources being smaller than a total number of the pixels.

8. An image-sensing apparatus as claimed in claim 7,

wherein the load resistors or constant-current sources each comprise a resistive transistor having a first electrode connected to the output signal line, a second electrode connected to a direct-current voltage, and a control electrode connected to a direct-current voltage.

5

9. An image-sensing apparatus as claimed in claim 8,

wherein the amplifying transistor is an N-channel MOS transistor, and

wherein a direct-current voltage applied to a first electrode of the amplifying transistor is higher than the direct-current voltage applied to the second electrode

10 of the resistive transistor.

10. An image-sensing apparatus as claimed in claim 8,

wherein the amplifying transistor is a P-channel MOS transistor, and

wherein a direct-current voltage applied to a first electrode of the amplifying

15 transistor is lower than the direct-current voltage applied to the second electrode of the resistive transistor.

11. An image-sensing apparatus as claimed in claim 1,

20 wherein the lead-out path includes a switch that selects one after another of the pixels in a predetermined sequence and feeds the signal output from the selected pixel to the output signal line.

12. An image-sensing apparatus as claimed in claim 1,

wherein the photoelectric conversion portion comprises:

the photosensitive element having a first electrode to which a direct-current voltage is applied and a second electrode;

a first transistor having a first electrode connected to the second electrode of the photosensitive element, a second electrode, and a control electrode,

5 the first transistor receiving an output current from the photoelectric element; and

a second transistor having a first electrode to which a direct-current voltage is applied, a second electrode from which an electric signal is output, and a control electrode connected to the first electrode of the first transistor, and

wherein the pixels each further comprise:

10 a first switching portion for applying a direct-current voltage to the control electrode of the first transistor; and

a second switching portion provided between the control electrode of the first transistor and the control electrode of the second transistor,

15 wherein the controller detects variations in sensitivity of the individual pixels by turning on the first switching portion and turning off the second switching portion so that a predetermined direct-current voltage is applied to the control electrode of the first transistor and that the control electrodes of the first and second transistors are brought into a cut-off state, and

20 wherein the controller makes the individual pixels perform image sensing by turning off the first switching portion and turning on the second switching portion so that the control electrodes of the first and second transistors are brought into a connected state.

13. An image-sensing apparatus as claimed in claim 12,

wherein the first switching portion is a third transistor having a first electrode connected to the control electrode of the first transistor, a second electrode to which a direct-current voltage is applied, and a control electrode,

wherein the second switching portion is a fourth transistor having a first
5 electrode connected to the control electrode of the first transistor, a second electrode connected to the control electrode of the second transistor, and a control electrode,

wherein the controller detects variations in sensitivity of the individual pixels by feeding a signal to the control electrode of the third transistor so as to turn
10 on the third transistor and turning off the fourth transistor so that a predetermined direct-current voltage is applied to the control electrode of the first transistor and that the control electrodes of the first and second transistors are brought into a cut-off state, and

wherein the controller makes the individual pixels perform image sensing by
15 turning off the third transistor and feeding a signal to the control electrode of the fourth transistor so as to turn on the fourth transistor so that the control electrodes of the first and second transistors are brought into a connected state.

14. An image-sensing apparatus as claimed in claim 1,

20 wherein, during image sensing, the pixels can each operate selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly and in a second state in which the photoelectric conversion portion converts the electric signal natural logarithmically.

15. An image-sensing apparatus as claimed in claim 12,

wherein, during image sensing, the pixels can each operate selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly and in a second state in which the photoelectric conversion portion
5 converts the electric signal natural logarithmically, and

wherein the controller switches the individual pixels between the first and second states by varying a voltage difference between the first and second electrodes of the first transistor of the photoelectric conversion portion of each pixel.

10 16. An image-sensing apparatus as claimed in claim 1,

wherein the controller detects variations in sensitivity of the photoelectric conversion portion of the individual pixels with the photosensitive elements of the individual pixels kept in a dark state.

15 17. An image-sensing apparatus comprising:

a plurality of pixels, the pixels each comprising:

a photodiode, having two electrodes, for producing an electric signal in accordance with amount of incident light;

20 a first MOS transistor having a first electrode connected to one of the electrodes of the photodiode, a second electrode, and a gate electrode;

a second MOS transistor having a first electrode connected to the gate electrode of the first MOS transistor, a second electrode to which a direct-current voltage is applied, and a gate electrode;

a third MOS transistor having a first electrode connected to the gate electrode of the first MOS transistor, a second electrode connected to the first electrode of the first MOS transistor, and a gate electrode; and

a fourth MOS transistor having a first electrode, a second electrode,
5 and a gate electrode connected to the first electrode of the first MOS transistor; and

a controller that detects variations in sensitivity of the individual pixels by feeding a signal to the gate electrode of the second MOS transistor so as to turn on the second MOS transistor and turning off the third MOS transistor so that a predetermined direct-current voltage is applied to the gate electrode of the first
10 MOS transistor and that the gate electrodes of the first and fourth MOS transistors are brought into a cut-off state,

wherein the controller makes the individual pixels perform image sensing by turning off the second MOS transistor and feeding a signal to the gate electrode of the third MOS transistor so as to turn on the third MOS transistor so that the gate
15 electrodes of the first and fourth MOS transistors are brought into a connected state.

18. An image-sensing apparatus as claimed in claim 17,

wherein, when making the individual pixels perform image sensing, the controller, in a case where the electric signal output from the photodiode is
20 converted natural-logarithmically and is output from the second electrode of the fourth MOS transistor, makes the first MOS transistor operate in a subthreshold region below a threshold value thereof, and, in a case where the electric signal output from the photodiode is converted linearly and is output from the second electrode of the fourth MOS transistor, brings a potential of the second electrode of

the first MOS transistor and a potential of the other electrode of the photodiode closer together so as to bring the first MOS transistor into an inactive state and, after allowing the electric signal to be output, performs resetting so that electric charges accumulated at the first and gate electrodes of the first MOS transistor are discharged by switching a level of a voltage applied to the gate electrode of the second MOS transistor so as to bring the second MOS transistor into a conducting state.

19. An image-sensing apparatus as claimed in claim 17,

wherein the pixels each further comprise a fifth MOS transistor having a first electrode connected to the second electrode of the fourth MOS transistor, a second electrode connected to an output signal line, and a gate electrode connected to a line select line.

20. An image-sensing apparatus as claimed in claim 17,

wherein the pixels each further comprise a sixth MOS transistor, having a first electrode to which a direct-current voltage is applied, a second electrode, and a gate electrode connected to the second electrode of the fourth MOS transistor, for amplifying an output signal output from the second electrode of the fourth transistor.

21. An image-sensing apparatus as claimed in claim 19,

wherein the pixels each further comprise a capacitor that is connected to a signal line of which one end is connected to the second electrode of the fourth

MOS transistor and that is reset through the fourth MOS transistor when a resetting voltage is fed to the first electrode of the fourth MOS transistor.

22. An image-sensing apparatus as claimed in claim 19,

5 wherein a direct-current voltage is applied to the first electrode of the fourth MOS transistor, and

wherein the pixels each further comprise:

10 a seventh MOS transistor having a first electrode connected to the second electrode of the fourth MOS transistor, a second electrode to which a direct-current voltage is applied, and a gate electrode; and

a capacitor that is connected to a signal line of which one end is connected to the second electrode of the fourth MOS transistor and that is reset through the seventh MOS transistor when a resetting voltage is fed to the gate electrode of the seventh MOS transistor.

15

23. An image-sensing apparatus as claimed in claim 17, further comprising:

MOS transistors connected by way of output signal lines to the individual pixels so as to serve as load resistors or constant-current sources.

20

24. An image-sensing apparatus as claimed in claim 17,

wherein the controller detects variations in sensitivity of the individual pixels with the photodiodes of the individual pixels kept in a dark state.

ABSTRACT OF THE DISCLOSURE

To reduce variations in output current of individual pixels resulting from variations in threshold voltage of the MOS transistor T1 provided in each pixel, the threshold voltage of the MOS transistor T1 of each pixel is measured to acquire
5 compensation data with which to correct the output current from the individual pixels. To acquire this compensation data, first, a MOS transistor T2 is turned on to apply a direct-current voltage VRB to the gate of the MOS transistor T1, and the MOS transistor T3 is turned off to disconnect the gates of the MOS transistors T1 and T4 from each other. Next, in this state, by turning a signal ϕ VPS first to a low
10 voltage and then to a voltage close to a direct-current voltage VPD, a negative electric charge is accumulated in the MOS transistor T1. A voltage resulting from this negative electric charge is applied to the gate of the MOS transistor T4, and thus the MOS transistor T5 is turned on, causing an output current to be fed to an output signal line 6 in accordance with the voltage applied to the gate of the MOS
15 transistor T4.

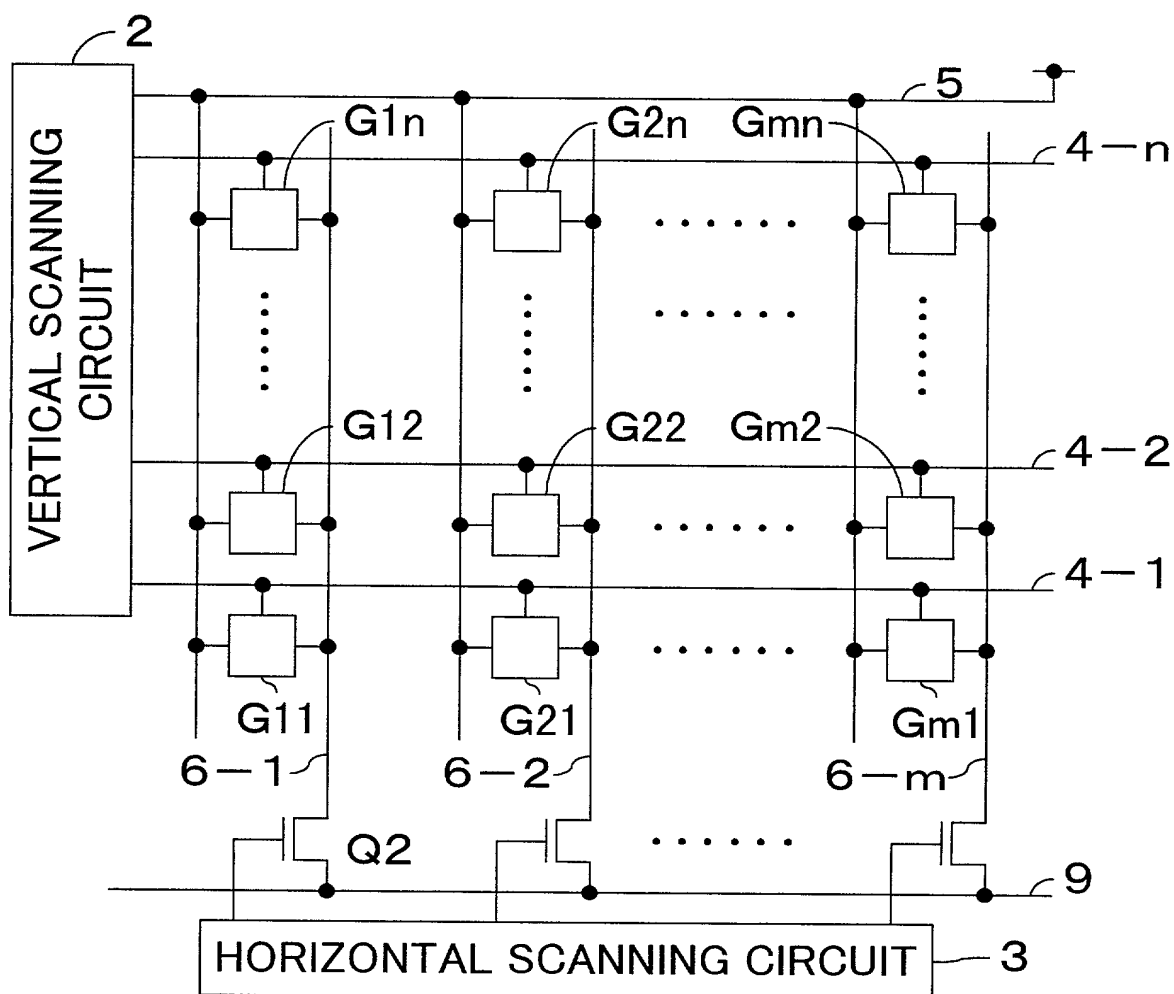
[illegible]

FIG.3

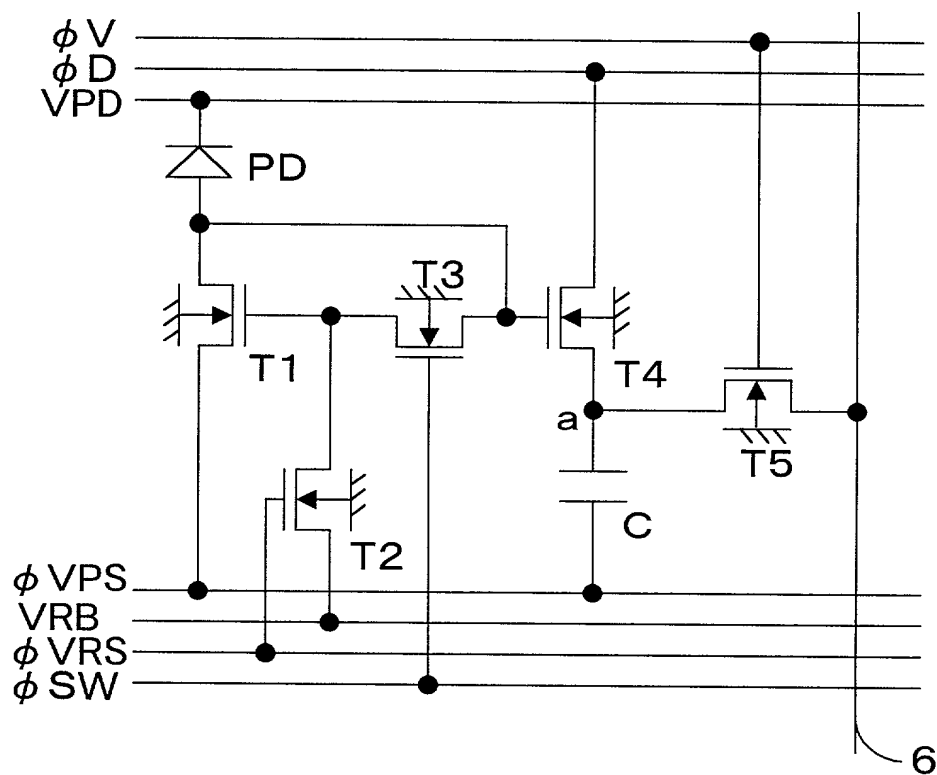


FIG.4A

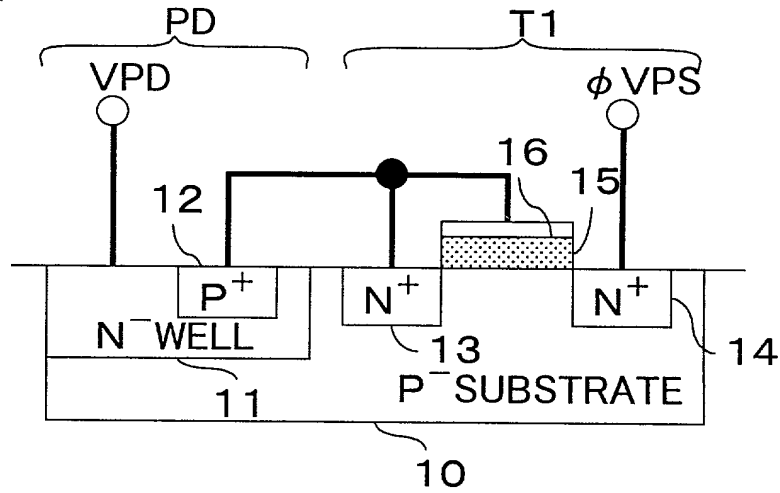


FIG.4B

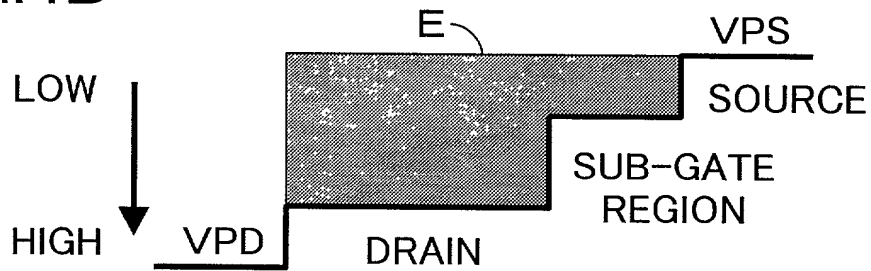
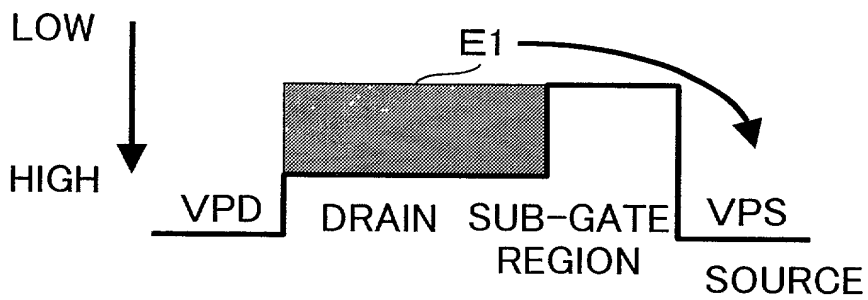


FIG.4C



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FIG.6

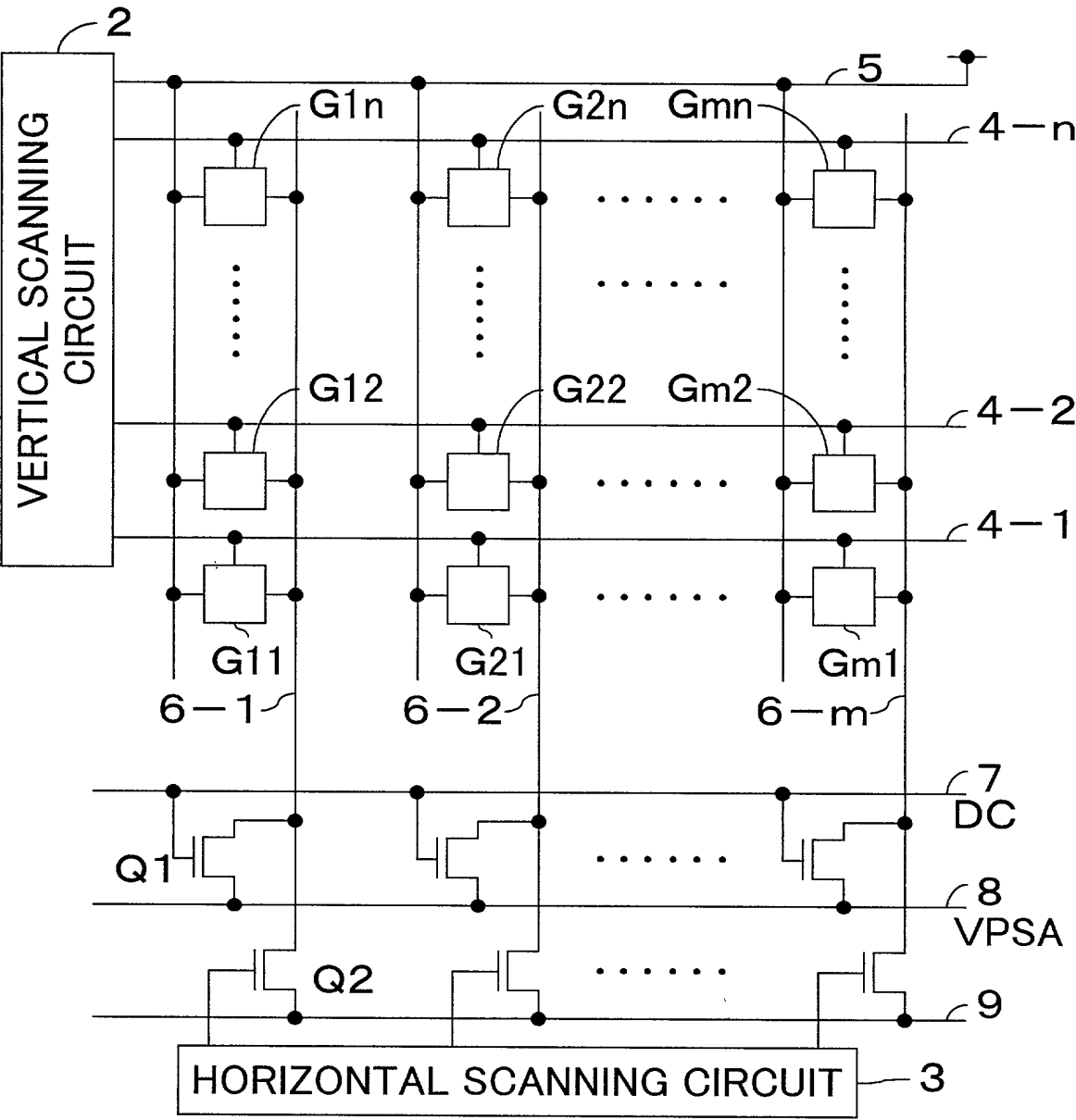


FIG.7A

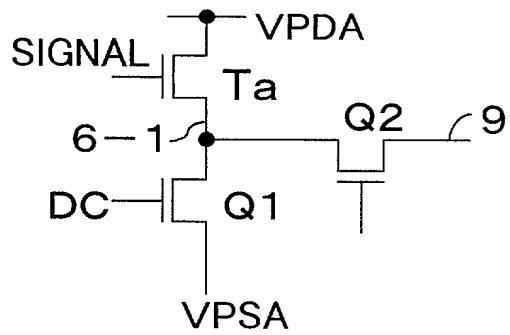


FIG.7B

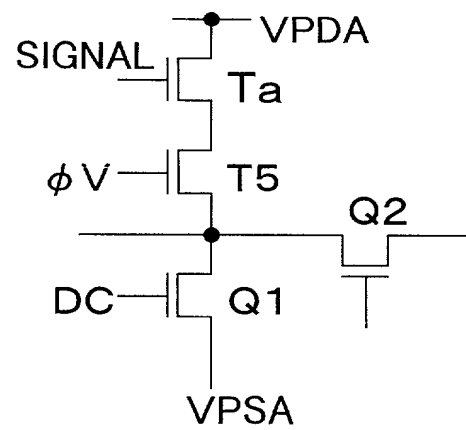


FIG.8

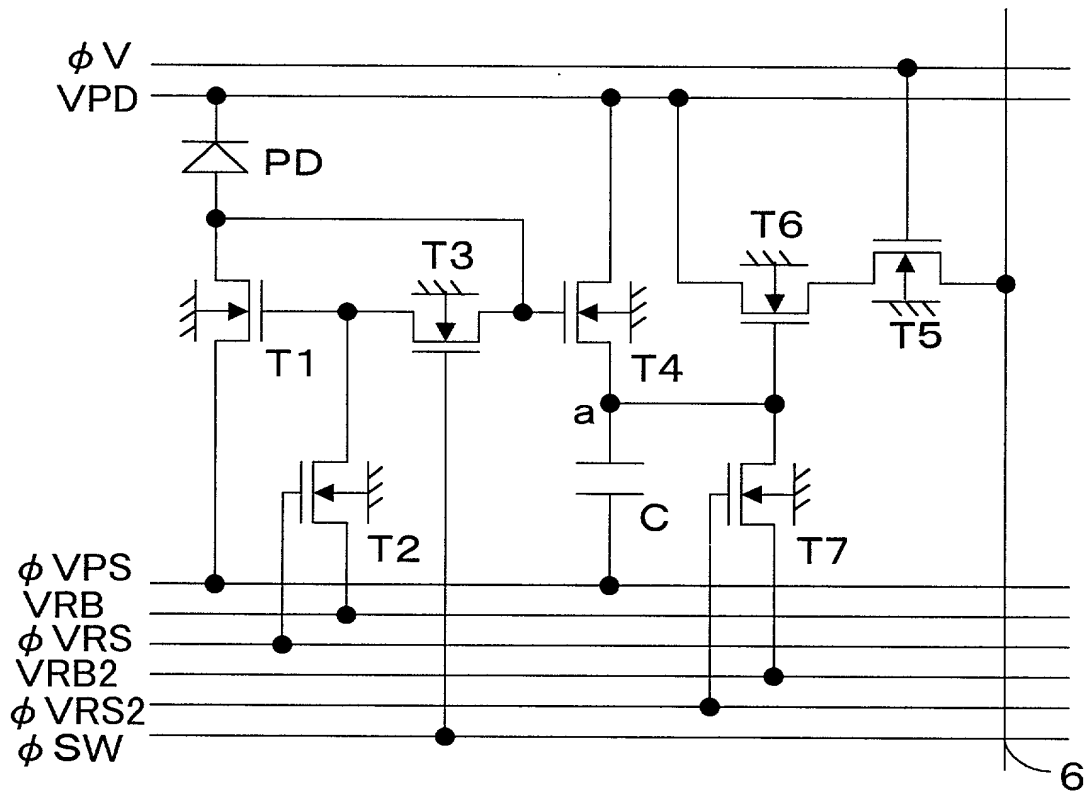


FIG.9

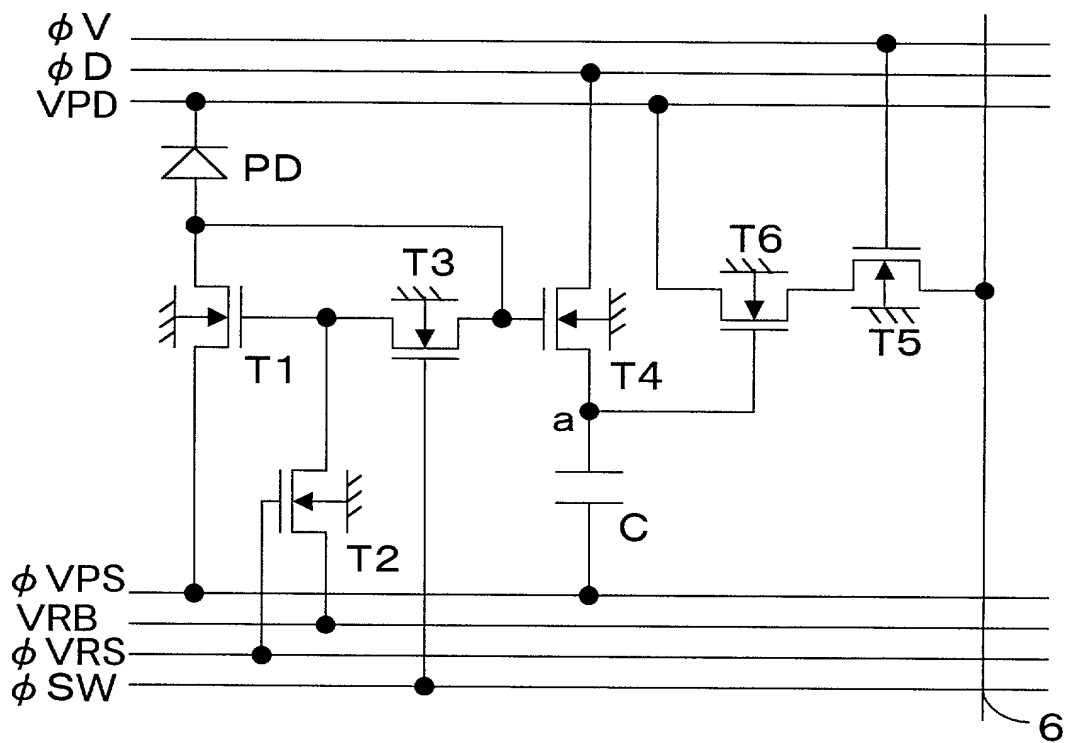
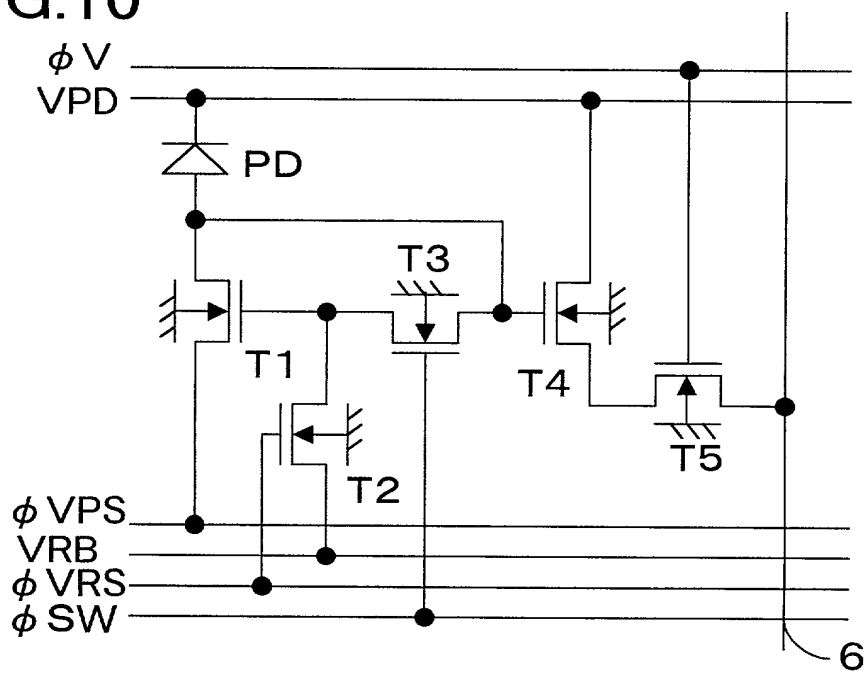


FIG.10



Variable	Mean	SD	Min	Max	Skewness	Kurtosis	Normality
Age	35.2	12.5	18	65	0.15	3.2	0.98
Gender	0.5	0.5	0	1	0.0	3.0	0.99
Marital Status	0.7	0.45	0	1	0.2	3.5	0.97
Education	12.5	2.5	9	16	0.1	3.1	0.99
Income	1500	800	500	3000	0.3	3.8	0.96
Health	0.8	0.4	0	1	0.1	3.2	0.98
Stress	4.5	1.5	1	7	0.2	3.3	0.97
Depression	2.5	1.0	1	5	0.1	3.1	0.99
Life Satisfaction	5.5	1.0	4	7	0.1	3.2	0.98
Resilience	3.5	1.0	1	5	0.2	3.4	0.96
Optimism	4.0	1.0	1	5	0.1	3.2	0.98
Self-Esteem	3.0	1.0	1	5	0.1	3.1	0.99
Loneliness	2.0	1.0	1	4	0.1	3.2	0.98
Loneliness (Control)	2.0	1.0	1	4	0.1	3.2	0.98
Stress (Control)	4.5	1.5	1	7	0.2	3.3	0.97
Depression (Control)	2.5	1.0	1	5	0.1	3.1	0.99
Life Satisfaction (Control)	5.5	1.0	4	7	0.1	3.2	0.98
Resilience (Control)	3.5	1.0	1	5	0.2	3.4	0.96
Optimism (Control)	4.0	1.0	1	5	0.1	3.2	0.98
Self-Esteem (Control)	3.0	1.0	1	5	0.1	3.1	0.99
Loneliness (Control)	2.0	1.0	1	4	0.1	3.2	0.98

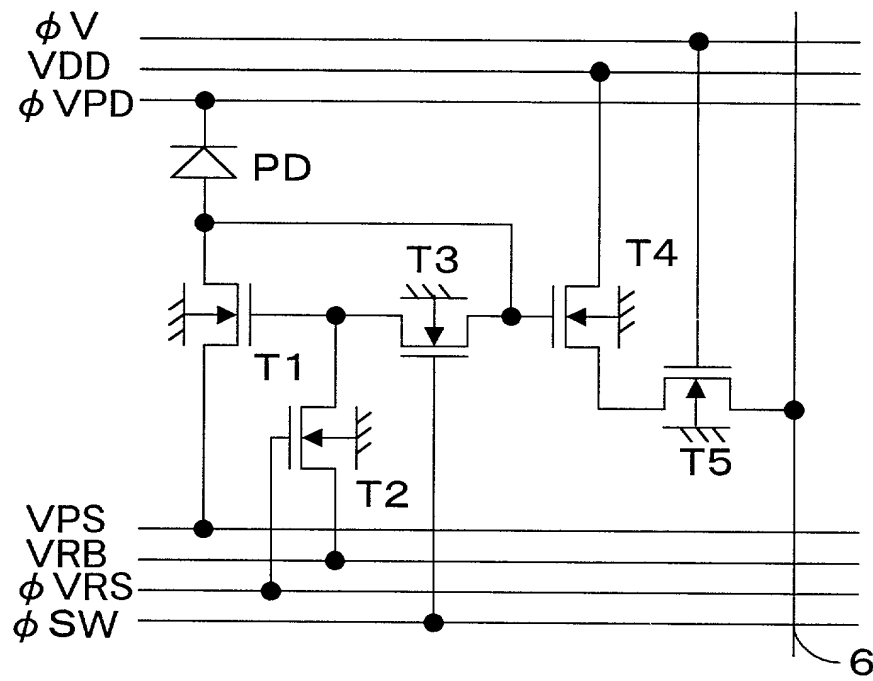


FIG.12

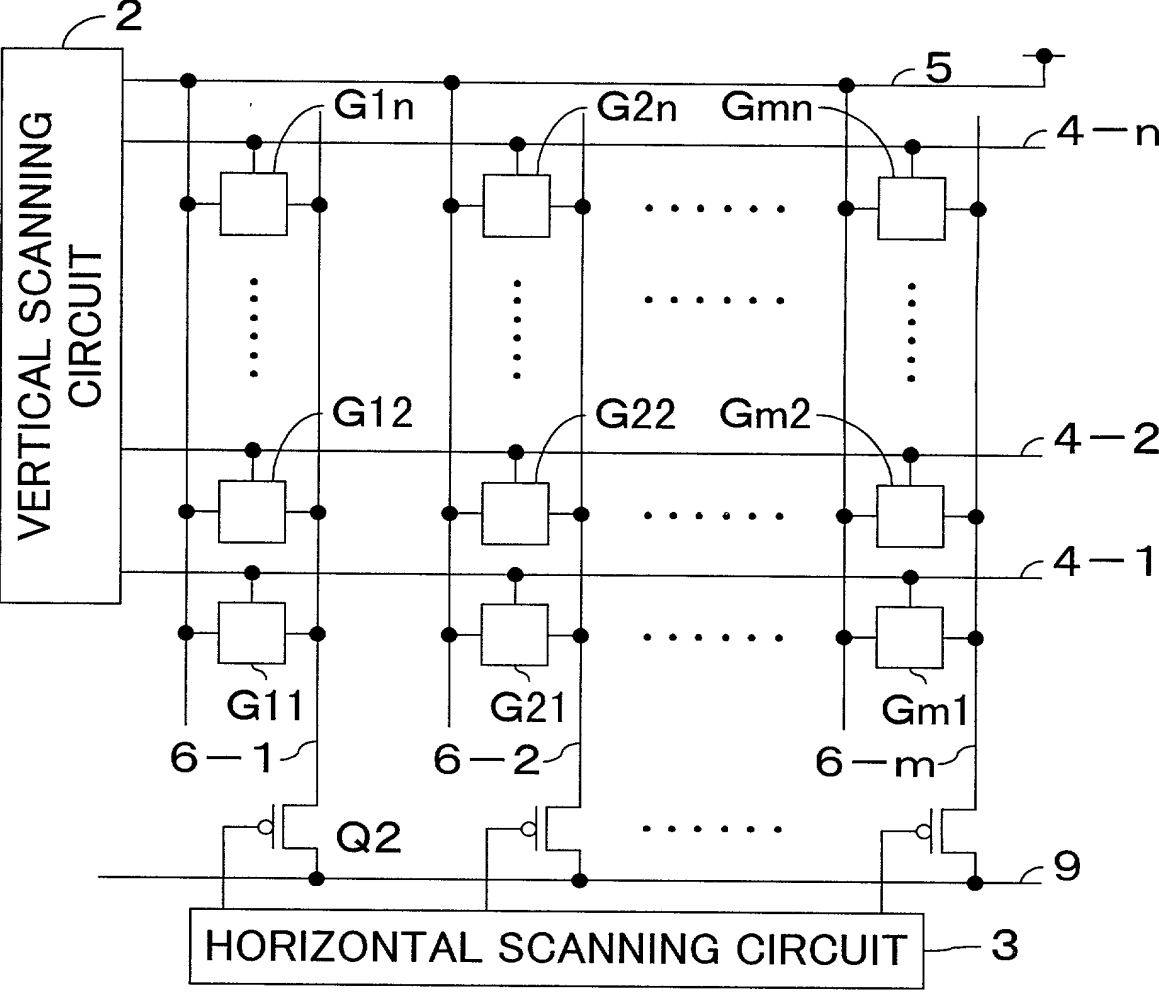


FIG.13

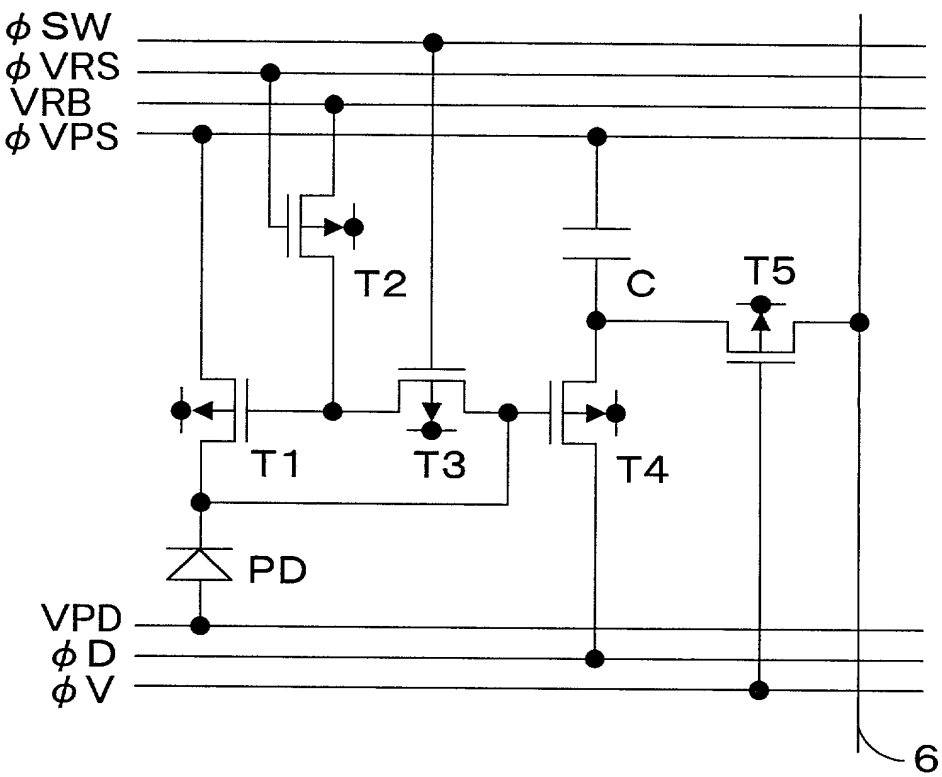


FIG.14

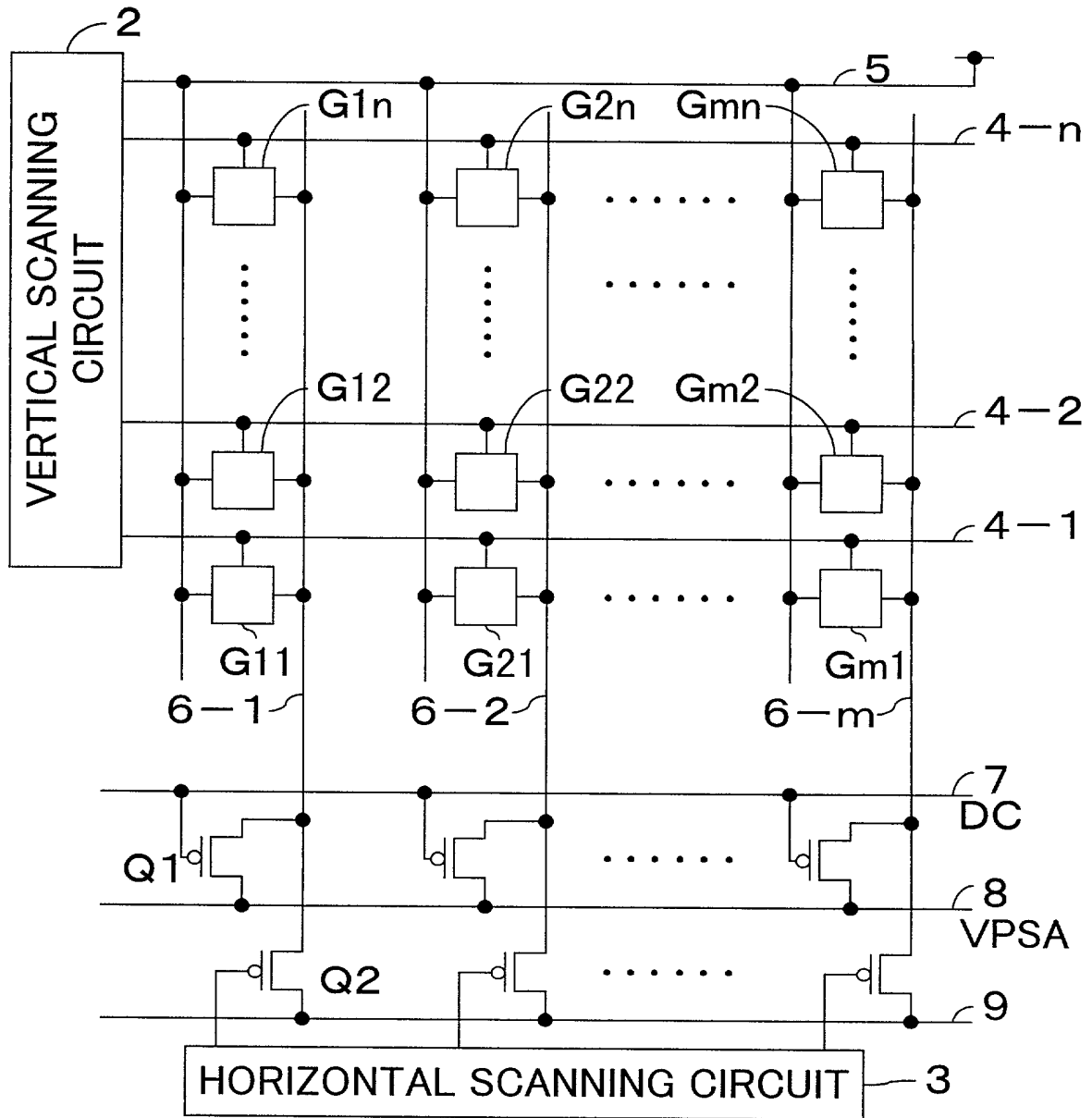


FIG.15A

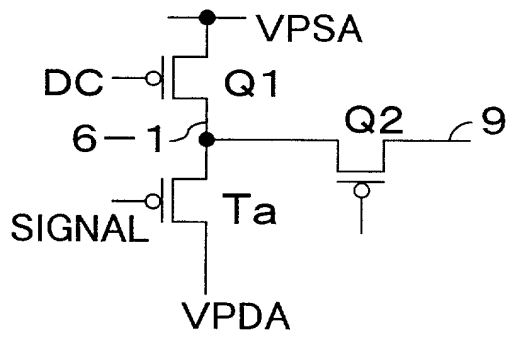


FIG.15B

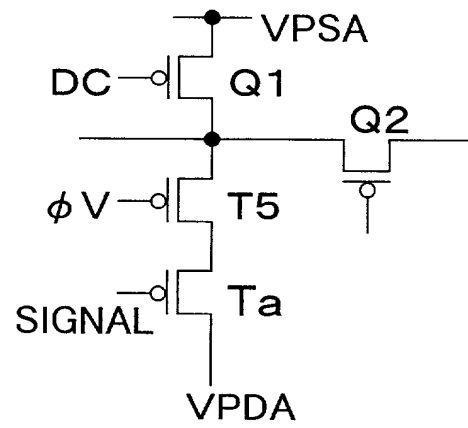


FIG.16

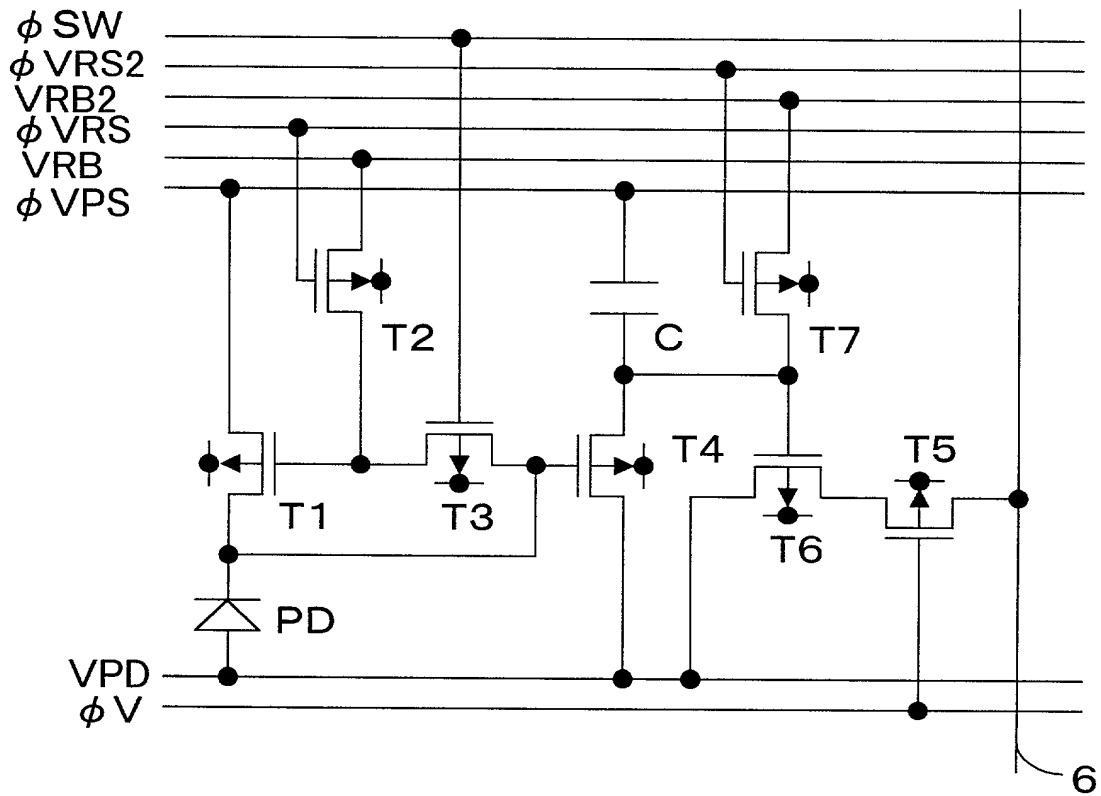


FIG.17

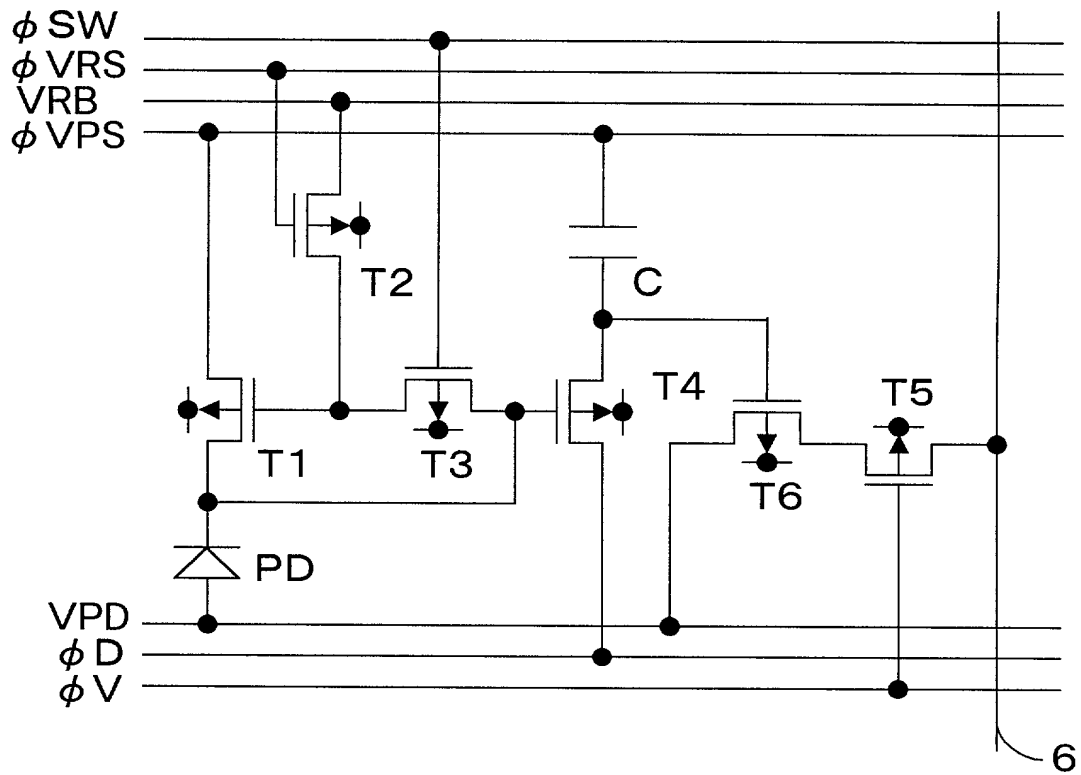


FIG.18

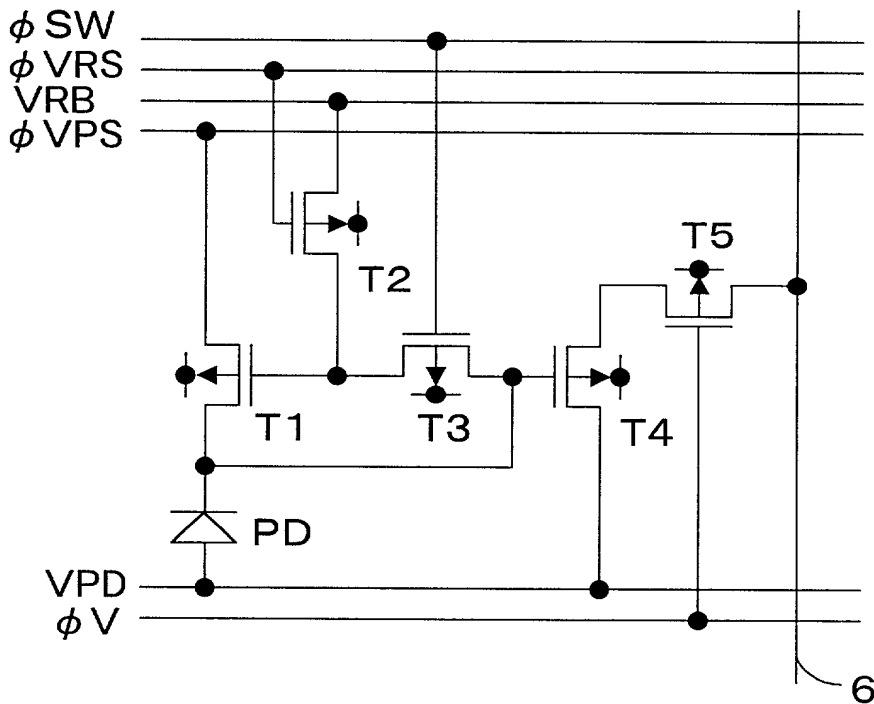


FIG.19

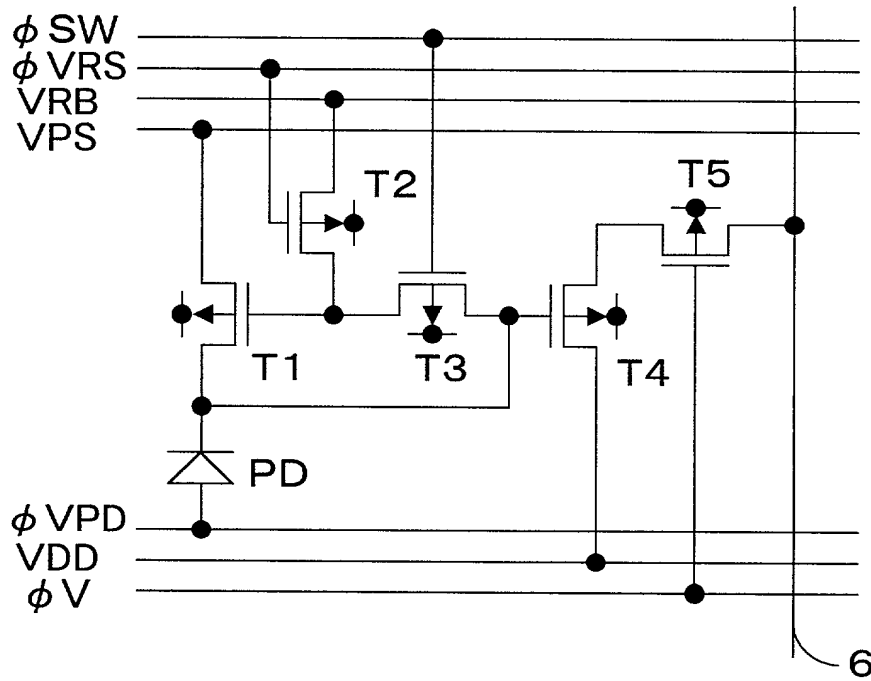


FIG.20

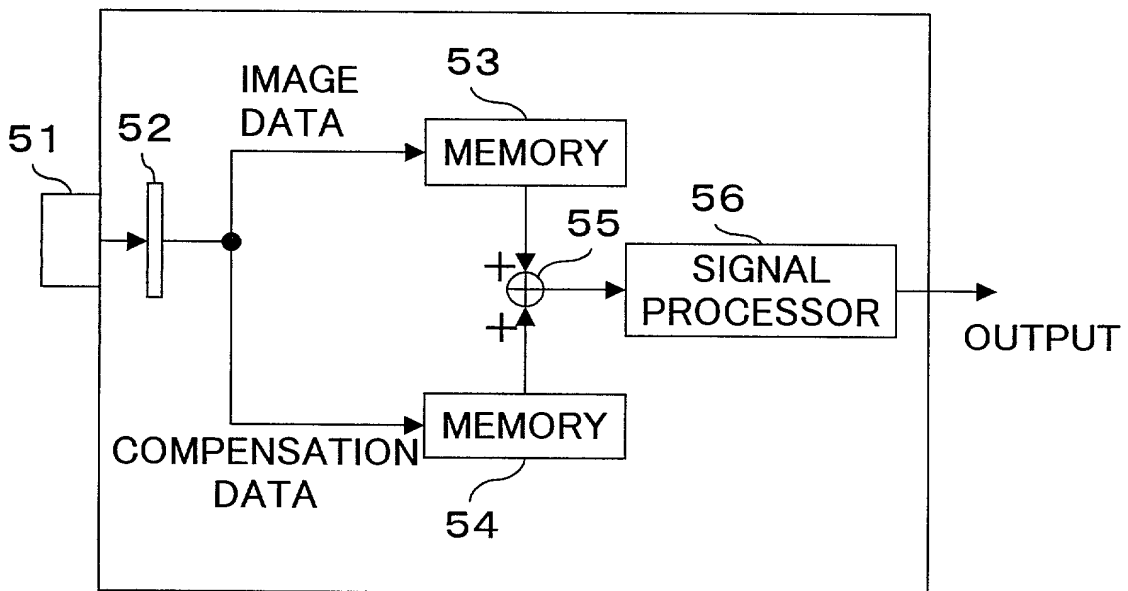
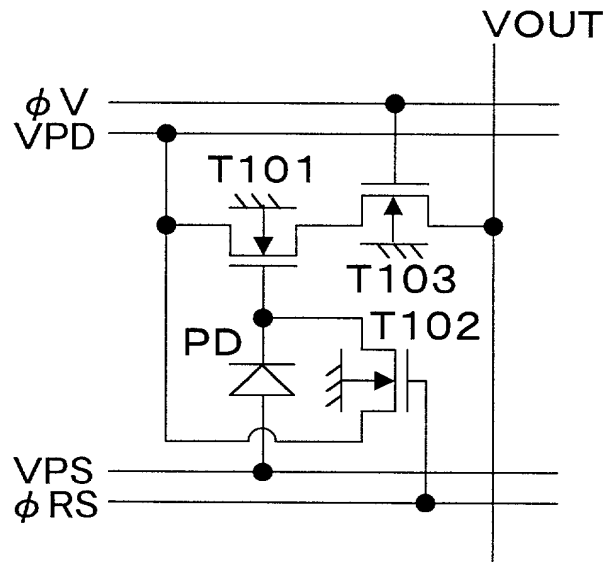


FIG.21

PRIOR ART



Attorney Docket No. _____

5

DECLARATION AND POWER OF ATTORNEY

FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

10

My residence, post office address and citizenship are as stated next to my name.

15

I believe I am the original, first and sole inventor (if only one name is listed below) or I and the other persons listed below are the original, first and joint inventors (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled
IMAGE-SENSING APPARATUS

20

the specification of which is attached hereto unless the following box is checked:

25

☐ was filed on _____
as United States Application Number or
PCT International Application Number
_____ and was amended on
_____ (if applicable).

30

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

5 I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56.

10 I hereby claim foreign priority under Title 35, United States Code, Section 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application
15 for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed.

PRIOR FOREIGN APPLICATION(S)

Priority

20 Not Claimed

H11-207411

Japan

22/07/1999

(Number)

(Country)

(Day/Month/Year Filed)

☐

25 _____
(Number)

(Country)

(Day/Month/Year Filed)

☐

(Number) (Country) (Day/Month/Year Filed) ☐

5

(Number) (Country) (Day/Month/Year Filed) ☐

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(Number) (Country) (Day/Month/Year Filed) ☐

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I hereby claim the benefit under Title 35, United States Code, Section 119(e) of any United States provisional application(s) listed below.

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(Application No.) (Filing Date)

(Application No.) (Filing Date)

I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of Title 35, United States Code Section 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, Section 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of application.

	_____ (Appl. No.)	_____ (Filing Date)	_____ (Status: Patented, Pending, Abandoned)
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	_____ (Appl. No.)	_____ (Filing Date)	_____ (Status: Patented, Pending, Abandoned)
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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the

Full name of sole or first inventor

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